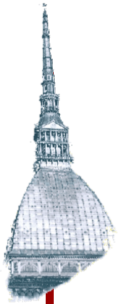


Tracciatori in 4D

Day 1:

- Why timing?
- A Time tagging system
- Gain in Silicon detectors
- Signal formation, go thin!

Day 2:

- Radiation damage
- Read-out
- From a pixel to a tracker

Bonus: design your own detector ➔ prepare for tomorrow

4D tracking with ultra-fast silicon detectors
http://iopscience.iop.org/article/10.1088/1361-6633/aa94d3/pdf
https://arxiv.org/abs/1704.08666

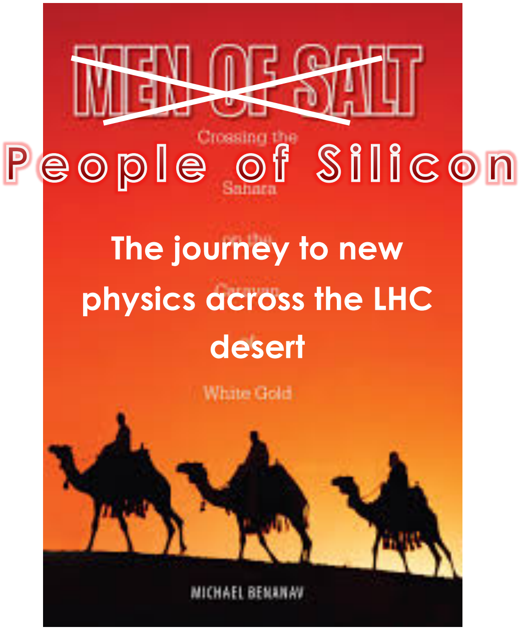
Preamble: Timing layers, 4D- and 5D-tracking

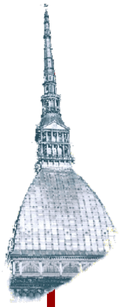
Besides a few indirect signals of new physics, particle physics today faces a discovery desert.

We need to cross an **energy- cross section** desert to reach the El-dorado of new physics.

Very little help in the direction of this path is coming from nature, the burden is on the accelerator and experimental physicists to provide the means for this crossing.

Timing is one of the enabling technologies to cross the desert





The effect of timing information

The inclusion of track-timing in the event information has the capability of changing radically how we design experiments.

Timing can be available at different levels of the event reconstruction, in increasing order of complexity:

1) Timing in the event reconstruction ➔ **Timing layers**
   - this is the easiest implementation, a layer ONLY for timing
2) Timing at each point along the track ➔ **4D tracking**
   - tracking-timing
3) Timing at each point along the track at high rate ➔ **5D tracking**
   - Very high rate represents an additional step in complication, very different read-out chip and data output organization

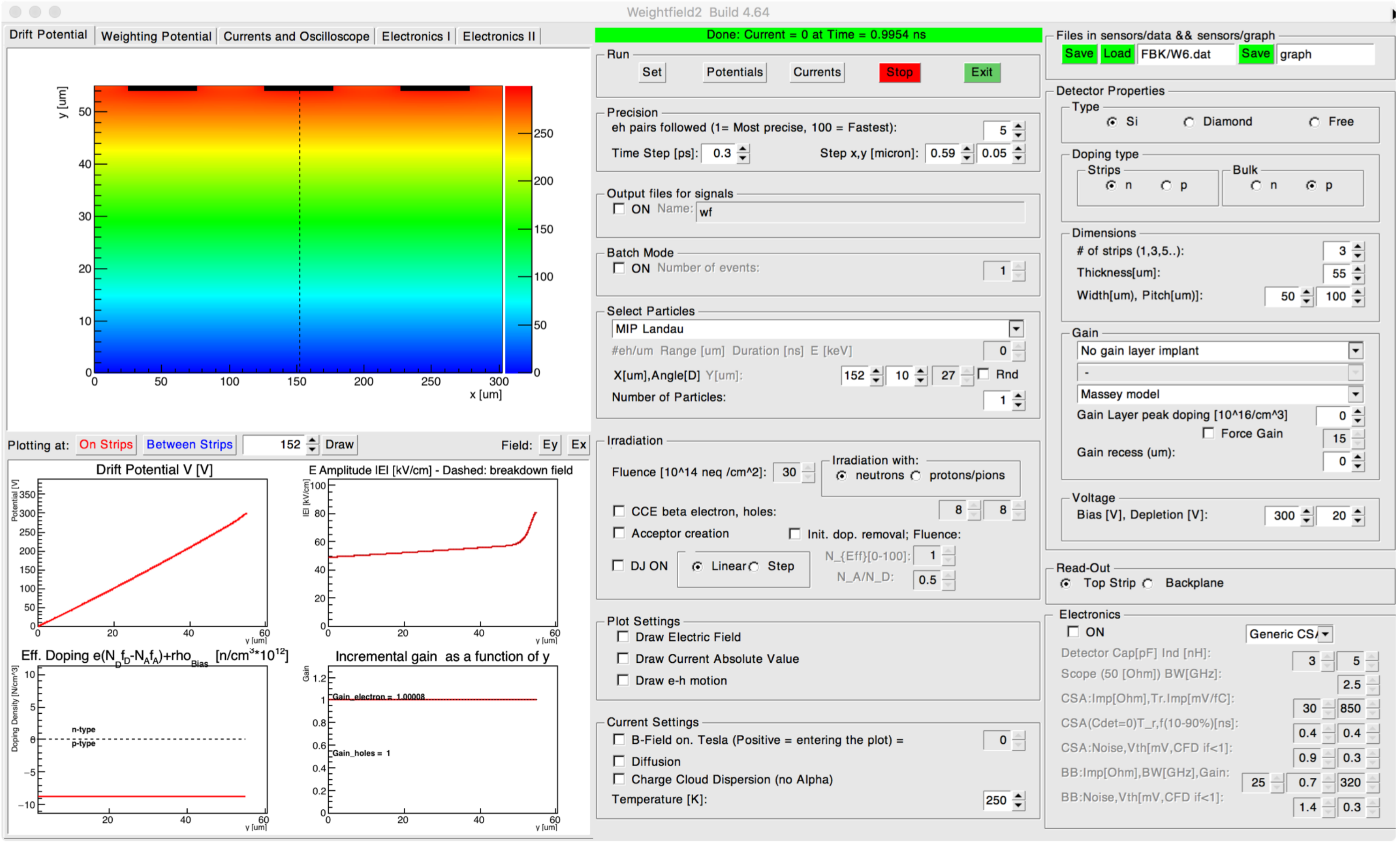
Preamble: simulator Weightfield2

Available at:

http://personalpages.to.infn.it/~cartigli/Weightfield2/Main.html

It requires Root build from source, it is for Linux and Mac.

It will not replace TCAD, but it helps in understanding the sensors response



Done: Current = 0 at Time = 0.9954 ns

Run

Precision
eh pairs followed (1= Most precise, 100 = Fastest): 5
Time Step [ps]: 0.3
Step x,y [micron]: 0.59 0.05

Output files for signals
☐ ON Name: wf

Batch Mode
☐ ON Number of events: 1

Select Particles
MIP Landau
#eh/um Range [um] Duration [ns] E [keV] 0
X[um],Angle[D] Y[um]: 152 10 27 ☐ Rnd
Number of Particles: 1

Irradiation
Fluence [10^14 neq /cm^2]: 30
Irradiation with: ● neutrons ○ protons/pions
☐ CCE beta electron, holes: 8 8
☐ Acceptor creation
☐ Init. dop. removal; Fluence:
☐ DJ ON ● Linear ○ Step
N_{Eff}[0-100]: 1
N_A/N_D: 0.5

Plot Settings
☐ Draw Electric Field
☐ Draw Current Absolute Value
☐ Draw e-h motion

Current Settings
☐ B-Field on. Tesla (Positive = entering the plot) = 0
☐ Diffusion
☐ Charge Cloud Dispersion (no Alpha)
Temperature [K]: 250

Files in sensors/data && sensors/graph
FBK/W6.dat
graph

Detector Properties
Type: ● Si ○ Diamond ○ Free
Doping type
Strips: ● n ○ p
Bulk: ○ n ● p
Dimensions
# of strips (1,3,5..): 3
Thickness[um]: 55
Width[um), Pitch[um)]: 50 100
Gain
No gain layer implant
-
Massey model
Gain Layer peak doping [10^16/cm^3] 0
☐ Force Gain 15
Gain recess (um): 0
Voltage
Bias [V], Depletion [V]: 300 20

Read-Out
● Top Strip ○ Backplane

Electronics
☐ ON
Generic CSA
Detector Cap[pF] Ind [nH]: 3 5
Scope (50 [Ohm]) BW[GHz]: 2.5
CSA:Imp[Ohm],Tr.Imp[mV/fC]: 30 850
CSA(Cdet=0)T_r,f(10-90%)[ns]: 0.4 0.4
CSA:Noise,Vth[mV,CFD if<1]: 0.9 0.3
BB:Imp[Ohm],BW[GHz],Gain: 25 0.7 320
BB:Noise,Vth[mV,CFD if<1]: 1.4 0.3

Weightfield2

Highlights:

- It is completely open source
- it's fast
- It generates the signal from several sources (MIP, alpha, lasers..)
- Runs in batch mode writing output files
- It loads/save configurations
- It has basics electronics simulation

It crashes occasionally

How to use it:

Obtain the last version from

http://personalpages.to.infn.it/~cartigli/Weightfield2/Main.html

1)From the download page, get the latest version
2)Unzip it and then type:
3)Make or 3-bis) make -f Makefile_MacOS10.10_root6
4)./weightfield

Consideriamo la situazione ad LHC, esperimento CMS

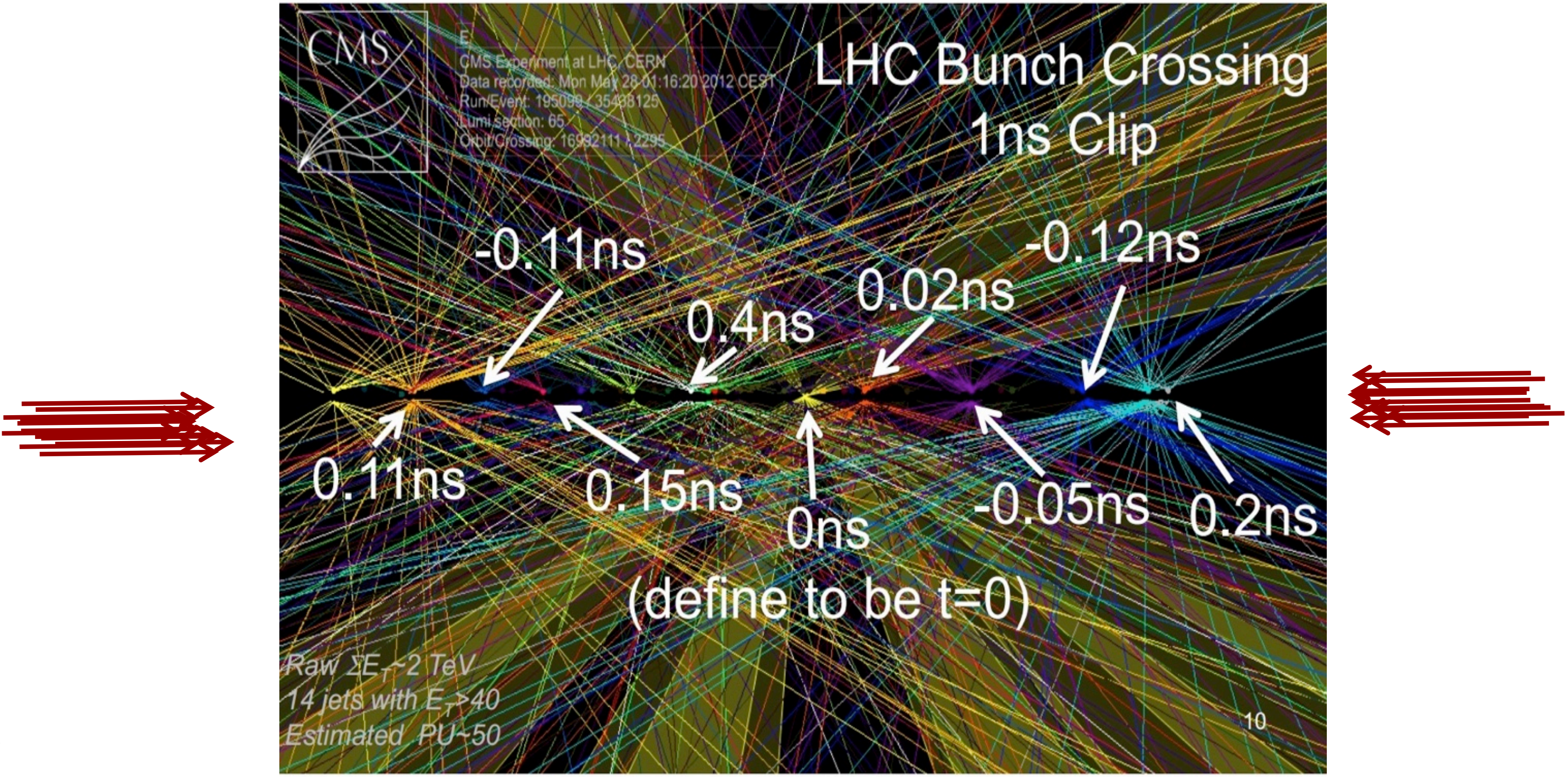
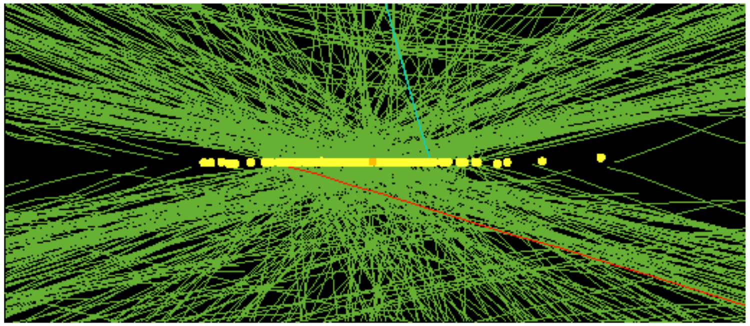


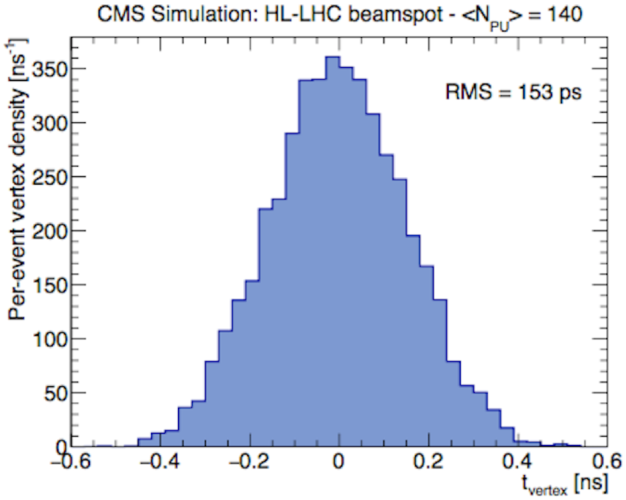
Figure 1 Interaction time of many proton-proton vertexes happening in the same bunch crossing in the case of ~ 50 overlapping events. The vertexes are spaced 10's of pico seconds apart.

Is timing really necessary?



The research into 4D tracking is strongly motivated by the HL-LHC experimental conditions:

150-200 events/bunch crossing



According to CMS simulations:

- **Time RMS between vertexes: 153 ps**
- **Average distance between two vertexes: 500 um**
- **Fraction of overlapping vertexes: 10-20%**
  - Of those events, a large fraction will have significant degradation of the quality of reconstruction

At HL-LHC: Timing is equivalent to additional luminosity

One extra dimension: tracking in 4Dimension

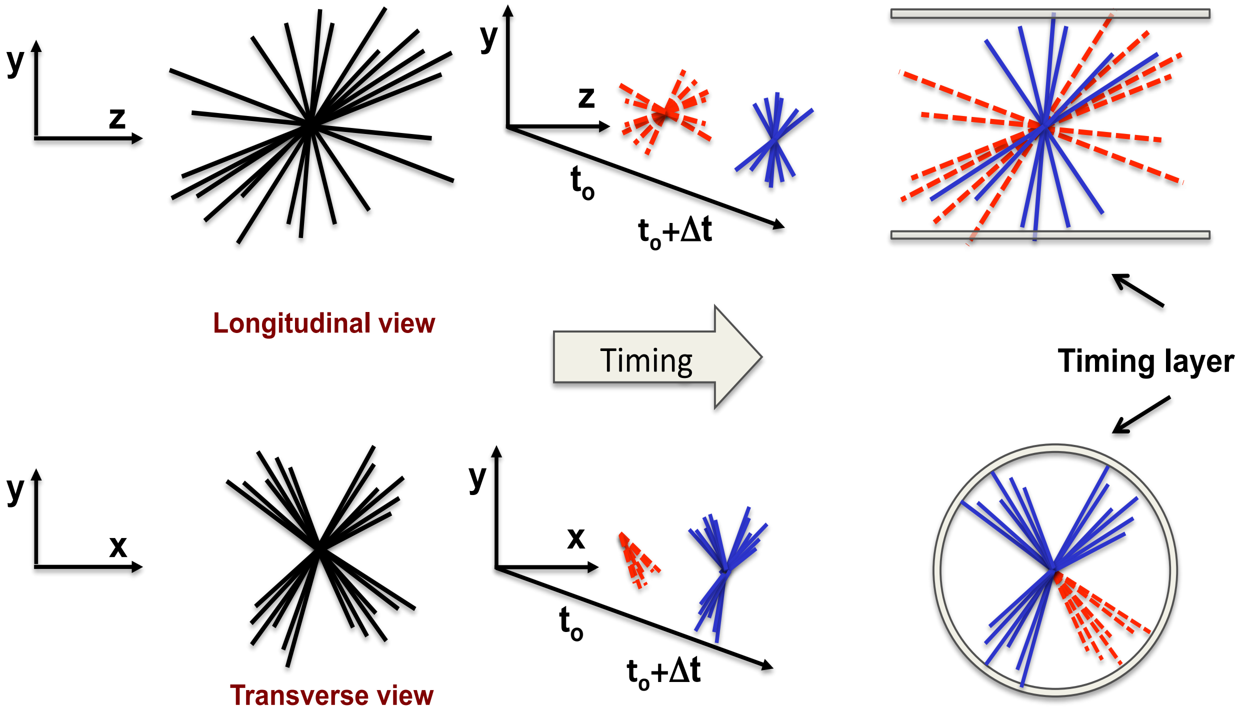
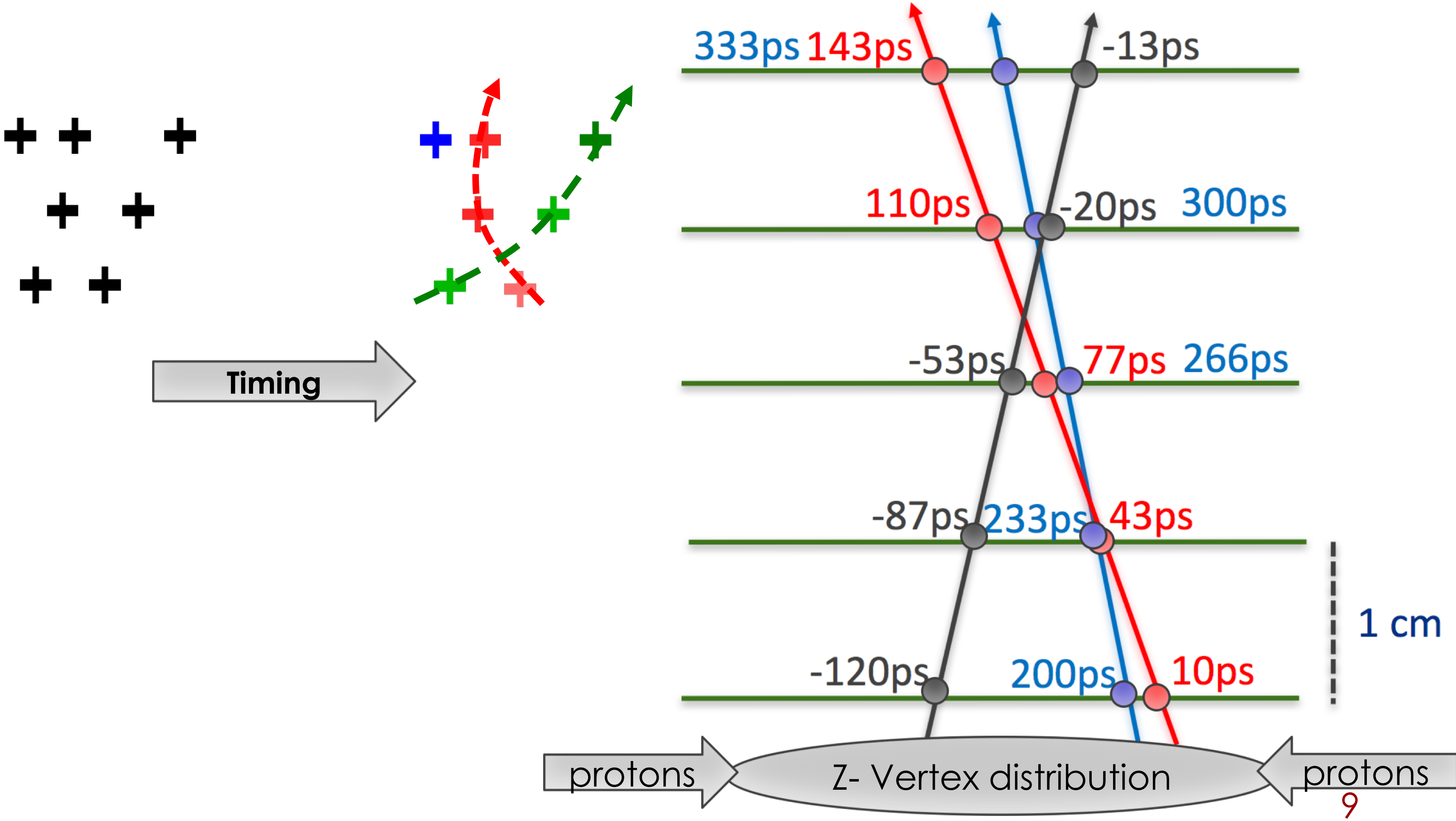


Figure 4 Schematic representation of the power of timing information in distinguishing overlapping events using a timing layer.

Timing at each point along the track

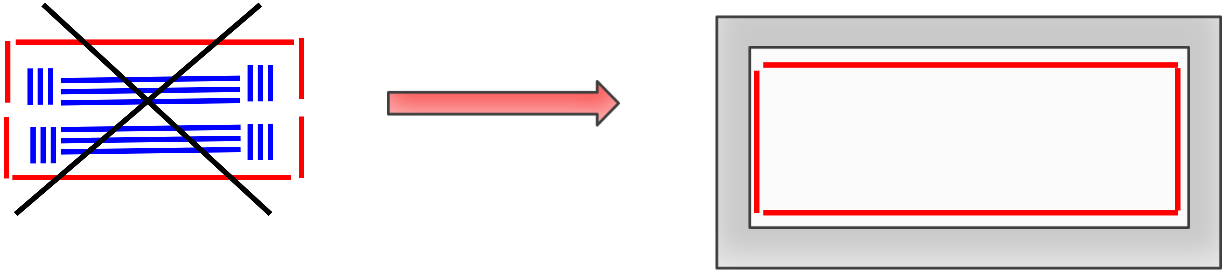
➔Massive simplification of patter recognition, new tracking algorithms will be faster even in very dense environments

➔ Use only "time compatible points"

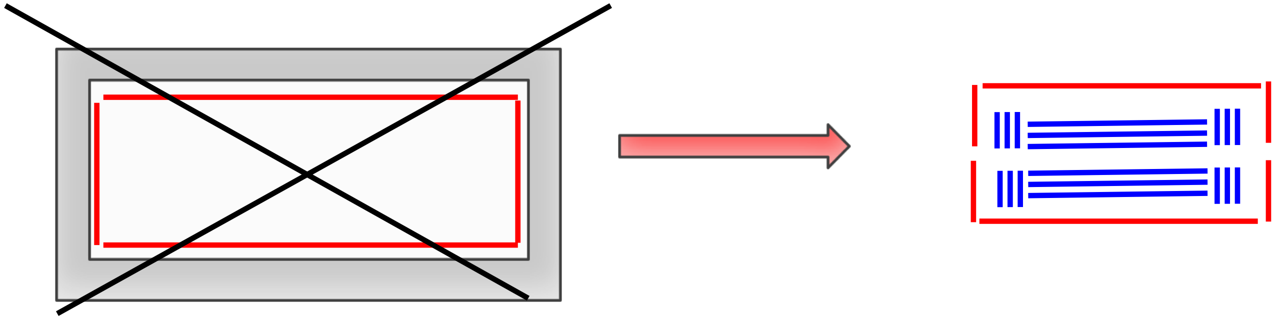


Where do we place a single timing layer?

The tracking community thinks it is a wonderful idea, clearly to be implemented **outside the tracker volume**, in front of the calorimeter



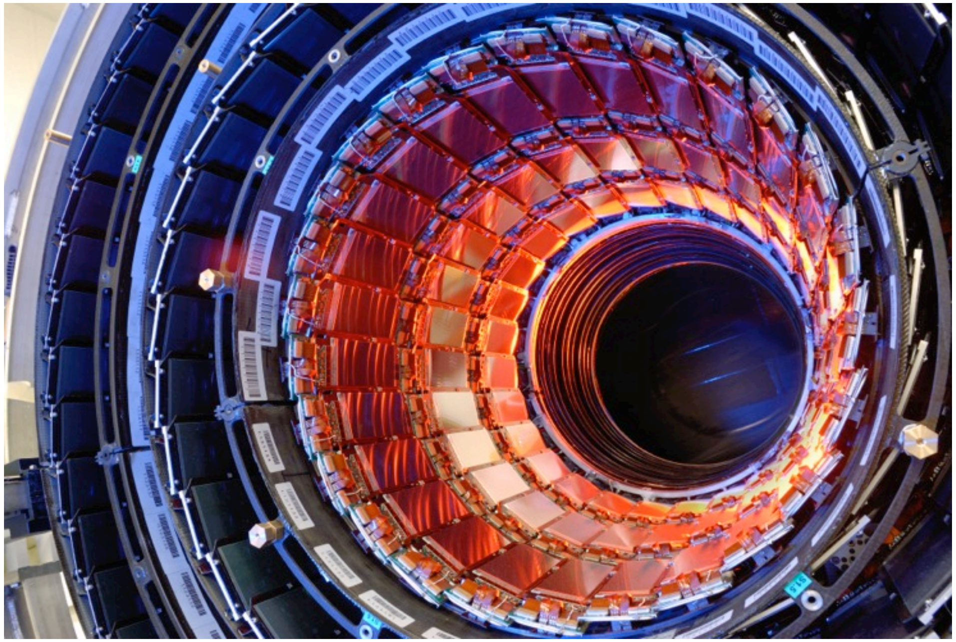
The calorimeter community thinks it is a wonderful idea, clearly to be implemented **far from the calorimeter,** in the tracker volume



We are now in contact with **the muon community….**

State-of-the-art Position Detectors

Extremely good position detectors are currently in use in every major high energy physics experiment:



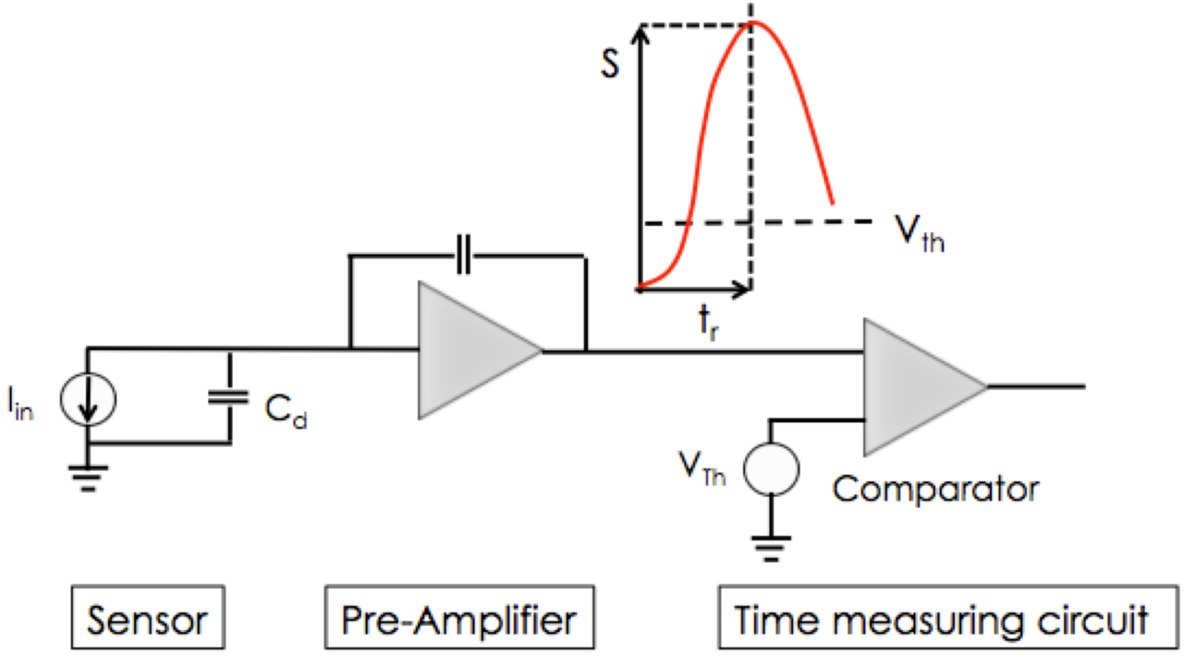
- Millions of channels
- Very reliable
- Very radiation hard

The timing capability is however limited to ~ 100-150 ps (NA62 @CERN)

σ_t ~ 100-150 ps
σ_x ~ 20-30 μm

Silicon time-tagging detector

(a simplified view)



Time is set when the signal crosses the comparator threshold

The timing capabilities are determined by the characteristics of the signal at the output of the pre-Amplifier and by the TDC binning.

Strong interplay between sensor and electronics

Time resolution

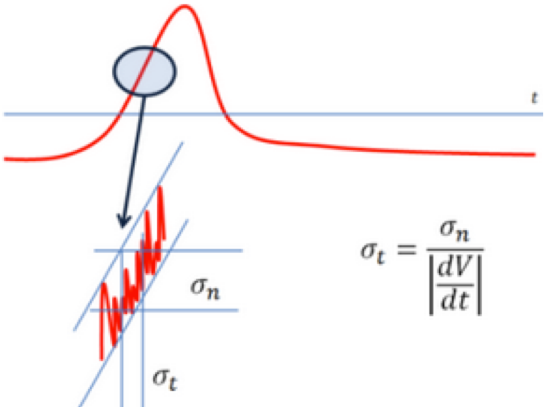
$$\sigma_t = \left(\frac{N}{dV/dt}\right)^2 + (\text{Landau Shape})^2 + \text{TDC}$$

Usual "Jitter" term

Here enters everything that is "Noise" and the steepness of the signal

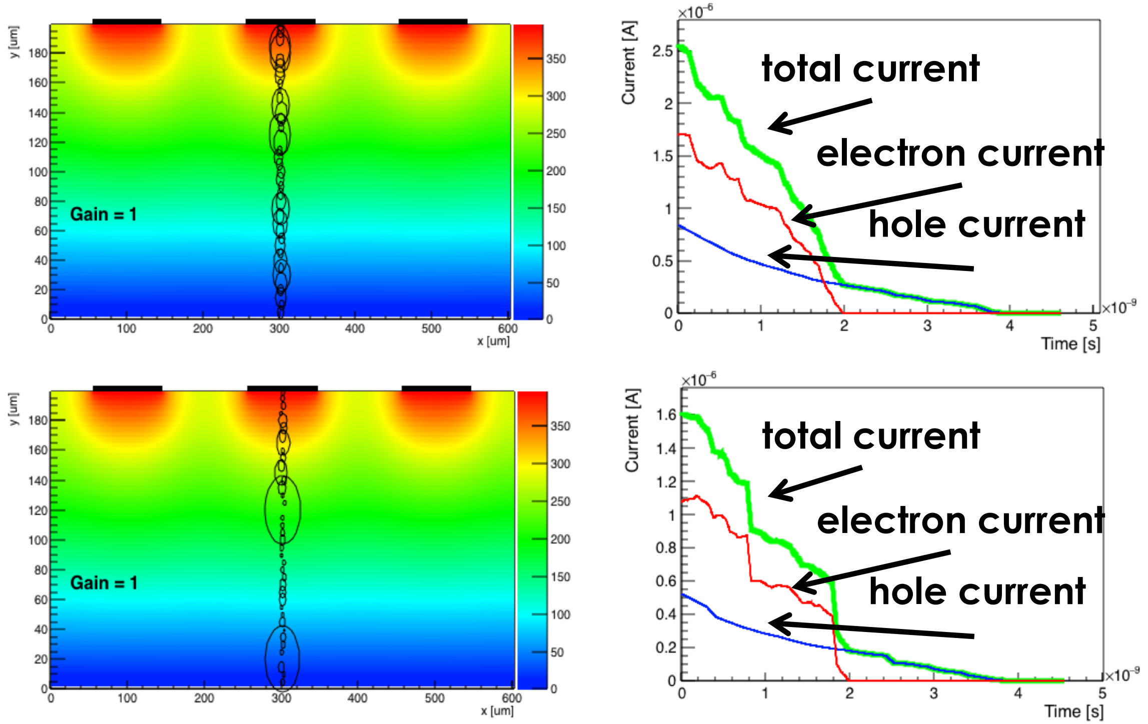
Time walk: Amplitude variation, corrected in electronics

Shape variations: non homogeneous energy



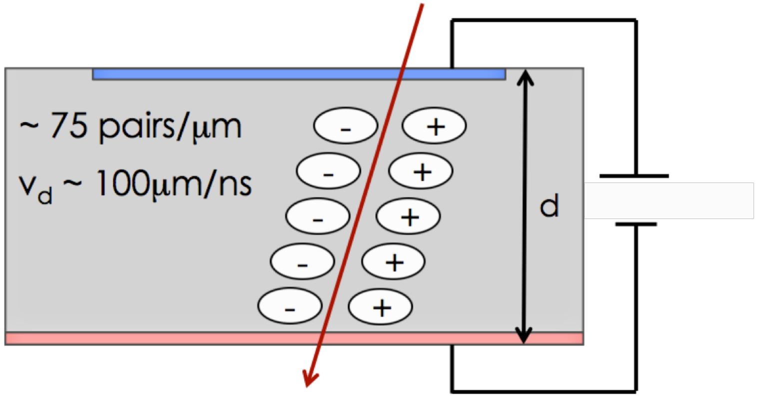
$$\sigma_t = \frac{\sigma_n}{\left|\frac{dV}{dt}\right|}$$

Need large dV/dt



Gain needs E ~ 300kV/cm. How can we do it?

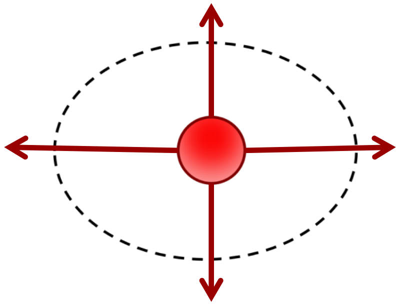
1) Use external bias: assuming a 50 micron silicon detector, we need $\mathbf{V_{bias}}$ **= ~ 600 - 700 V**



Difficult to achieve

2) Use Gauss Theorem:

$$\sum q = 2\pi r * E$$



E = 300 kV/cm ➔ q ~ 10^{16} /cm³

Need to have 10^{16}/cm³ charges !!

Gain in Silicon detectors

Gain in silicon detectors is commonly achieved in several types of sensors. It's based on the avalanche mechanism that starts in high electric fields: V ~ 300 kV/cm

Charge multiplication

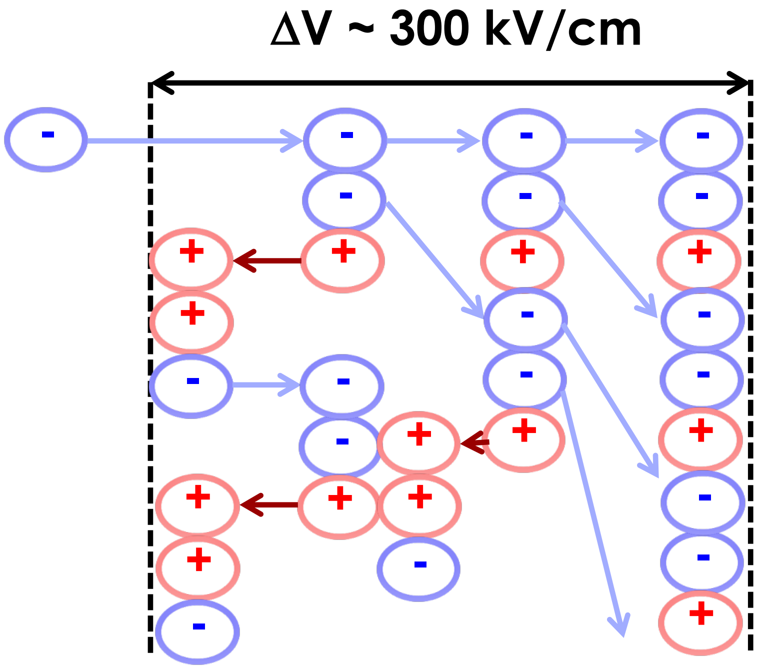
$$N(l) = N_0 \cdot e^{\alpha \cdot l}$$

Gain:

$$G = e^{\alpha\, 1}$$

$$\alpha_{e,h}(E) = \alpha_{e,h}(\infty) * \exp\left(-\frac{b_{e,h}}{|E|}\right)$$

α = strong E dependance
α ~ 0.7 pair/µm for electrons,
α ~ 0.1 for holes



Concurrent multiplication of electrons and holes generate very high gain

Silicon devices with gain:

- **APD: gain 50-500**
- **SiPM: gain ~ 10^4**

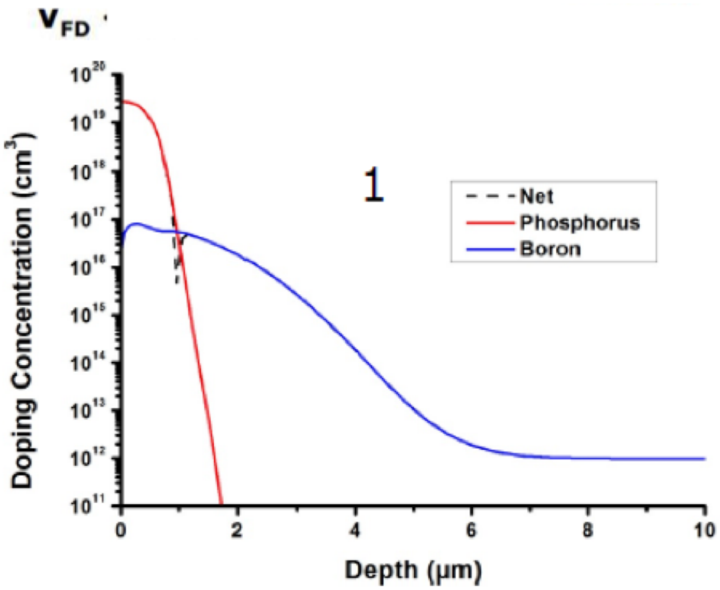
Low Gain Avalanche Detectors (LGADs)

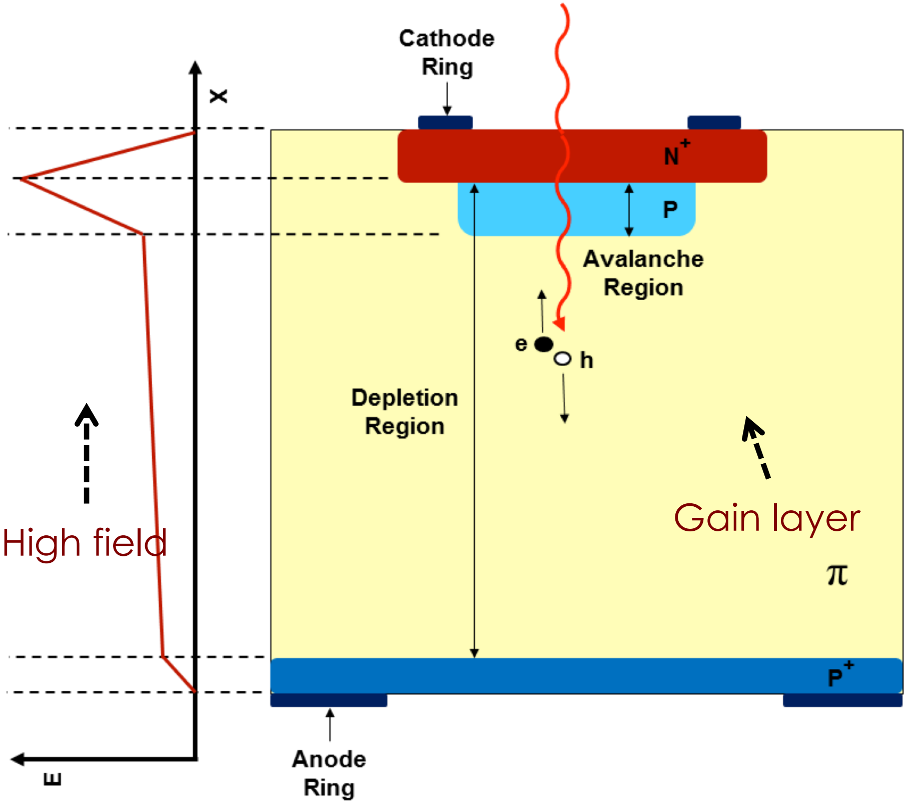
The LGAD sensors, as proposed and manufactured by CNM

(National Center for Micro-electronics, Barcelona):

High field obtained by adding an extra doping layer

E ~ 300 kV/cm, closed to breakdown voltage

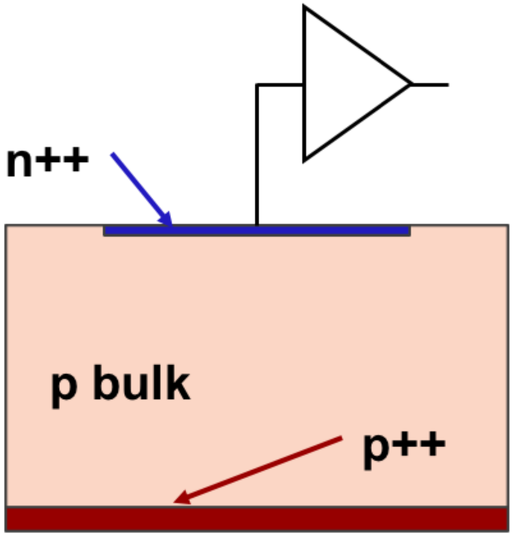




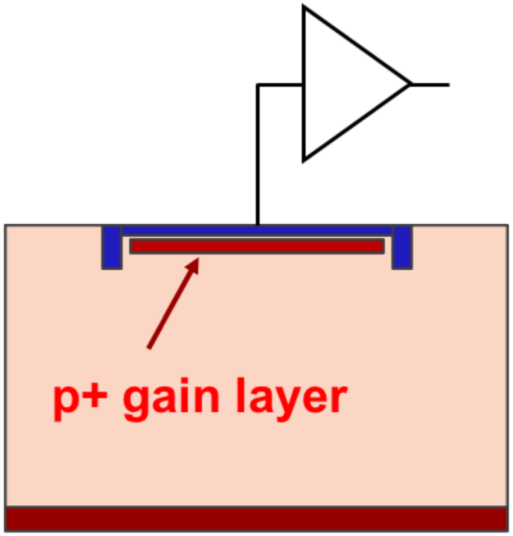
High field

Gain layer

Difference PiN - LGAD



Traditional silicon diode



Low Gain Avalanche Diode

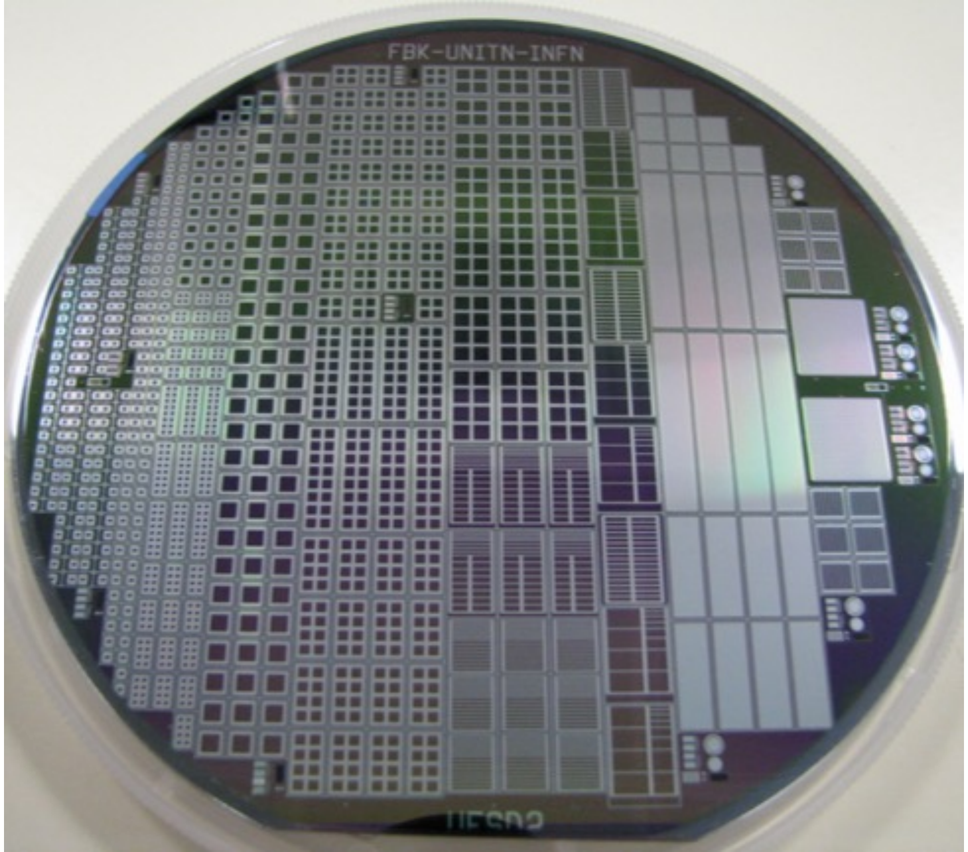
Come di fanno dei sensori?

Collaborazione molto intensa (~ una riunione a settimana per 3 anni…)

FBK – Trento Uni – INFN

UFSD1: 300-micron. First LGAD production at FBK. Gain layer study, edges

UFSD2: 50-micron. Very successful, good gain and overall behavior, excellent time resolution. Gain layer doping: Boron, Gallium, Boron + Carbon, Gallium+Carbon



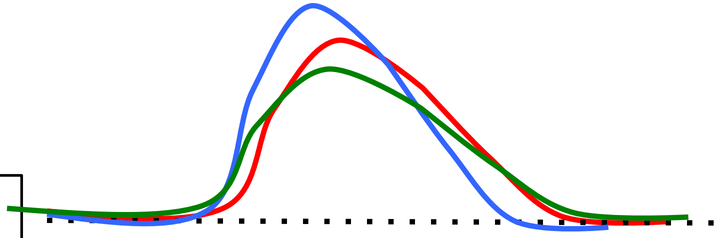
Not all geometries are possible

Signal shape is determined by Ramo's Theorem:

$$i \propto qvE_w$$

Drift velocity

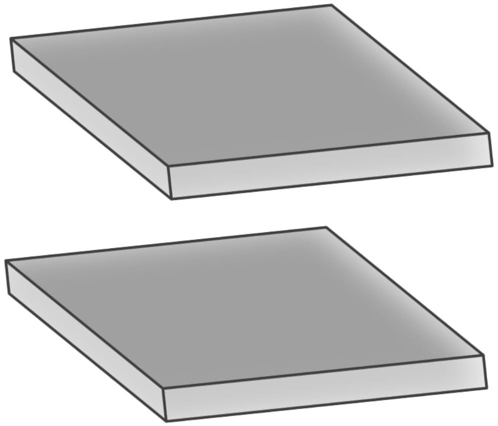
Weighting field



The key to good timing is the uniformity of signals:

Drift velocity and Weighting field need to be as uniform as possible

Basic rule: parallel plate geometry



Drift Velocity

$$i \propto q\boxed{v}E_w$$

- ➔ Highest possible E field to saturate velocity
- ➔ Highest possible resistivity for velocity uniformity

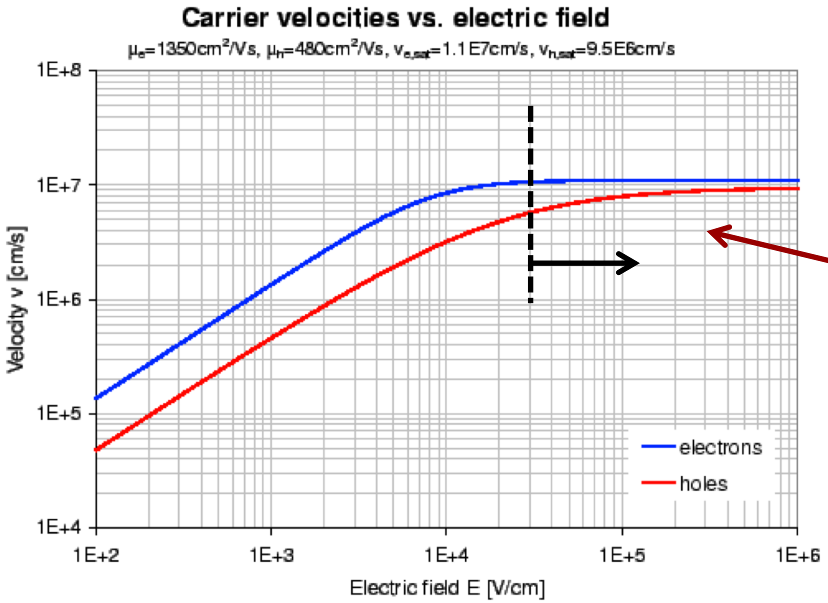


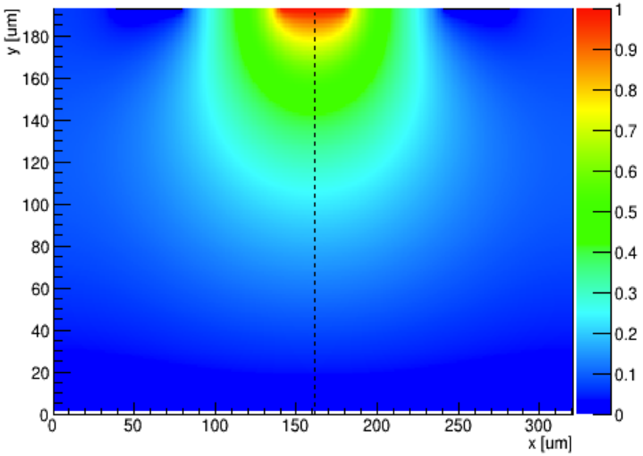
Figure: Electron and hole velocities vs. the electric field strength in silicon.

We want to operate in this regime

Weighting Field: coupling the charge to the electrode

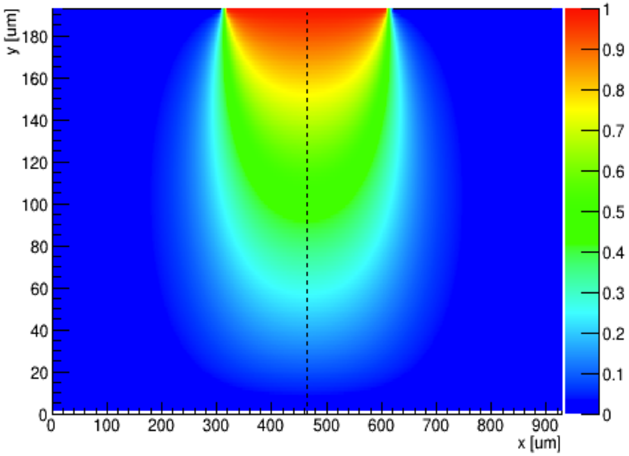
$$i \propto qv\boxed{E_w}$$

Strip: 100 μm pitch, 40 μm width



Bad: almost no coupling away from the electrode

Pixel: 300 μm pitch, 290 μm width



Good: strong coupling almost all the way to the backplane

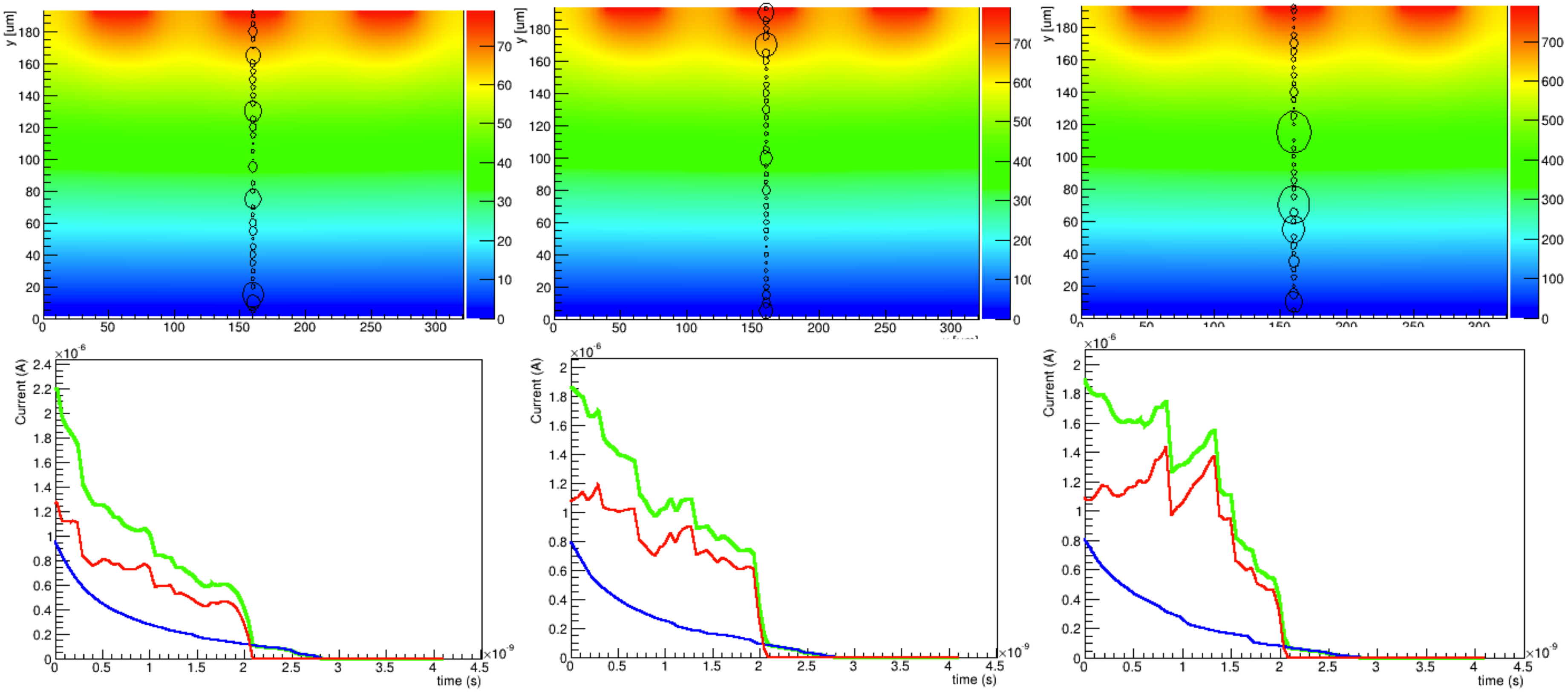
The weighting field needs to be as uniform as possible, so that the coupling is always the same, regardless of the position of the charge

Non-Uniform Energy deposition

Landau Fluctuations cause two major effects:

- Amplitude variations, that can be corrected with time walk compensation
- For a given amplitude, the charge deposition is non uniform.

These are 3 examples of this effect:

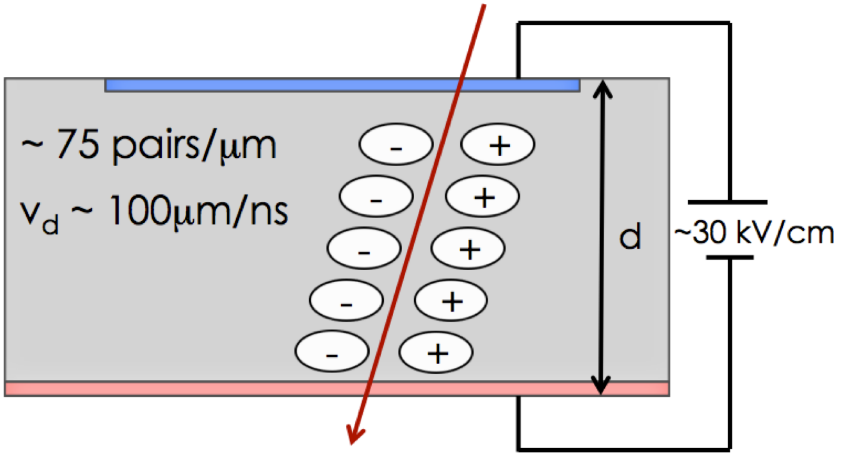


Signal formation in silicon detectors

We know we need a large signal, but **how is the signal formed?**

What is controlling the slew rate?

$$\frac{dV}{dt} \propto ?$$



A particle creates charges, then:

- The charges start moving under the influence of an external field
- The motion of the charges induces a current on the electrodes
- The signal ends when the charges reach the electrodes

What is the signal of one e/h pair?

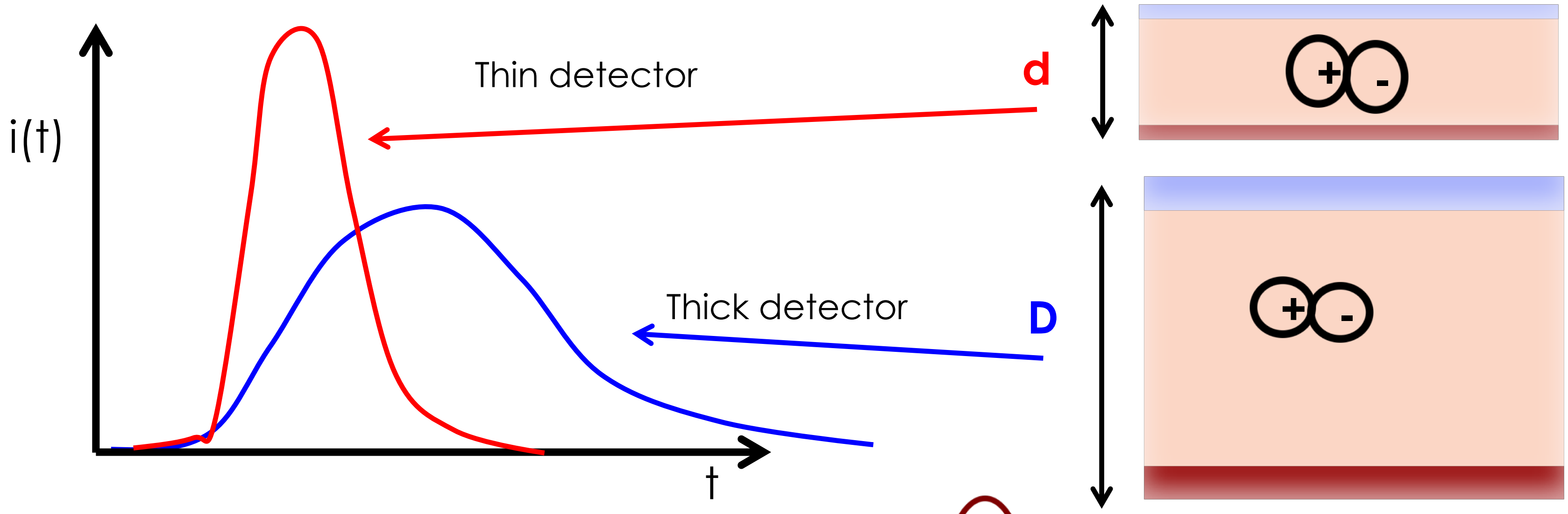
(Simplified model for pad detectors)

Let’s consider **one single electron-hole pair.**

The integral of their currents is equal to the electric charge, q:

$$\int [i_{el}(t)+i_h(t)]dt = q$$

However **the shape of the signal depends on the thickness** d: thinner detectors have higher slew rate



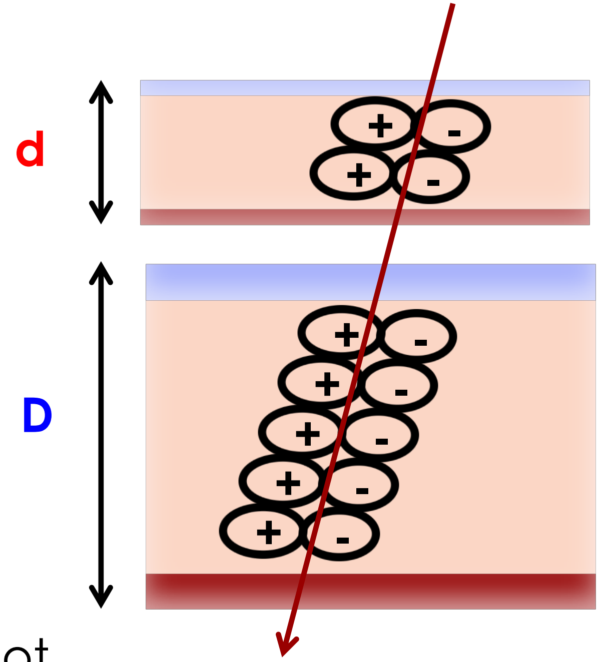
➔ One e/h pair generates higher current in thin detectors

$$i \propto qv\frac{1}{d}$$

Weighting field

Large signals from thick detectors?

(Simplified model for pad detectors)



Thick detectors have higher number of charges:

$$Q_{tot} \sim 75\ q*d$$

However each charge contributes to the initial current as:

$$i \propto qv\frac{1}{d}$$

The initial current for a silicon detector does not depend on how thick (d) the sensor is:

$$i = Nq\frac{k}{d}v = (75\cancel{d}q)\frac{k}{\cancel{d}}v = 75kqv \sim 1-2*10^{-6}A$$

Number of e/h = 75/micron

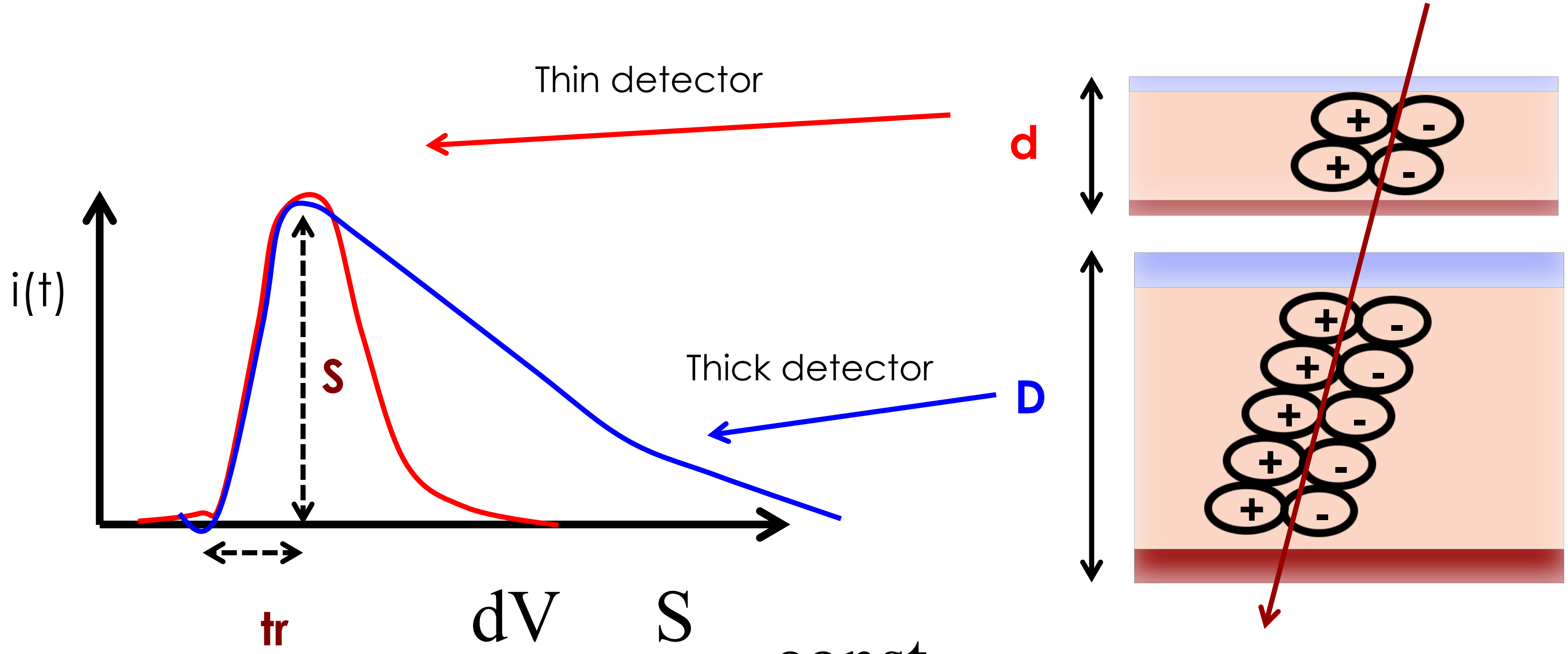
Weighting field

velocity

➔ Initial current = constant

Thin vs Thick detectors

(Simplified model for pad detectors)

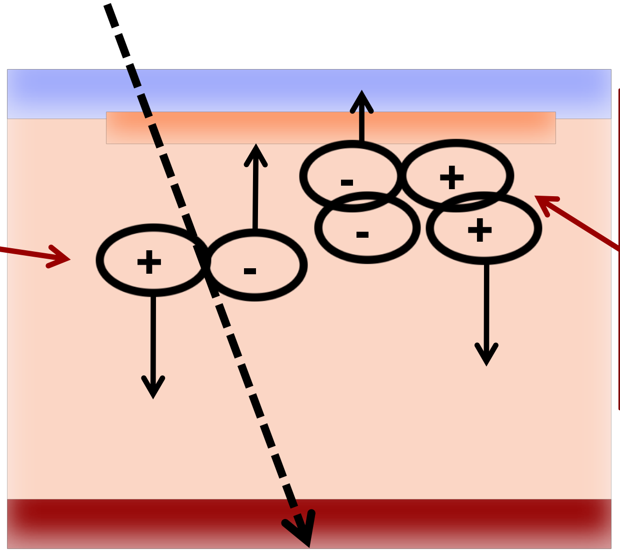


$$\frac{dV}{dt} \sim \frac{S}{t_r} \sim \text{const}$$

Thick detectors have longer signals, not higher signals

We need to add gain

How gain shapes the signal



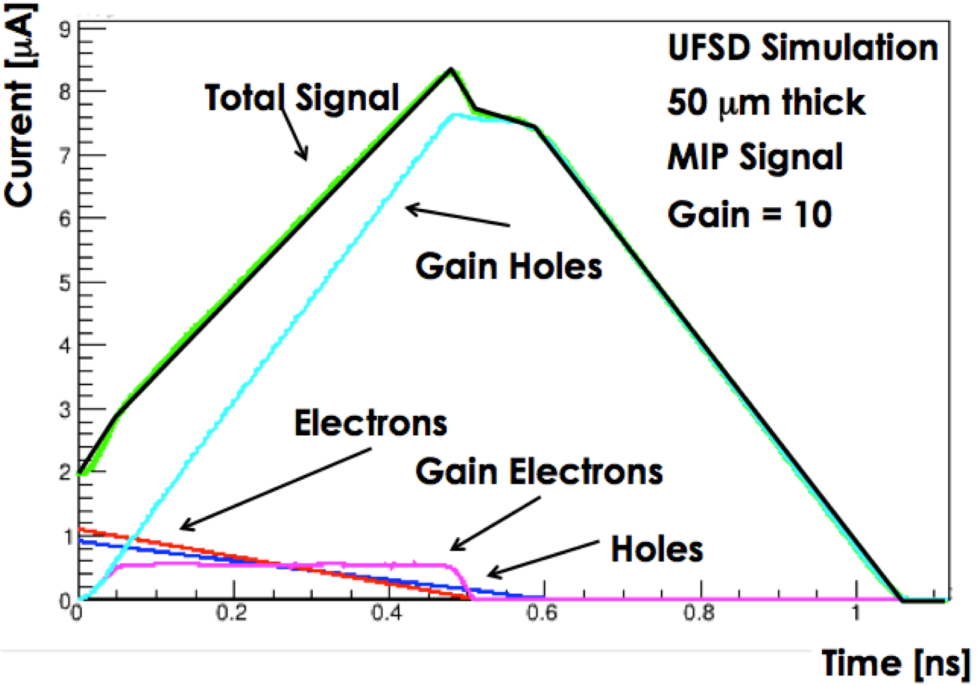
Initial electron, holes

Gain electron:

absorbed immediately

Gain holes:

long drift home



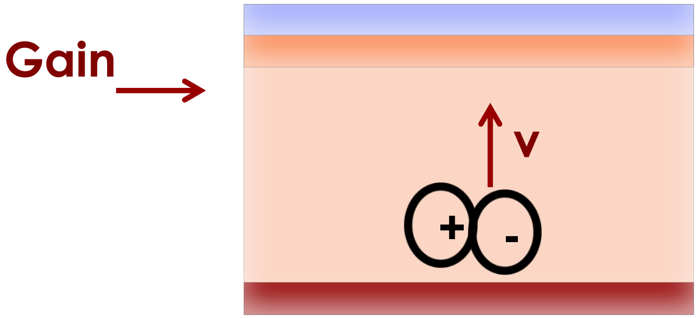
Electrons multiply and produce additional electrons and holes.

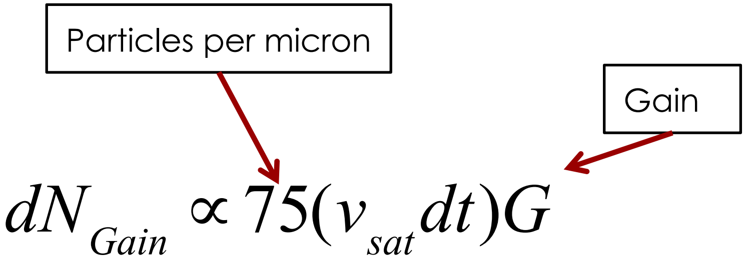
- **Gain electrons have almost no effect**
- **Gain holes dominate the signal**

➔ **No holes multiplications**

Interplay of gain and detector thickness

The rate of particles produced by the gain does not depend on *d* (assuming saturated velocity v_{sat})





$$dN_{Gain} \propto 75(v_{sat}dt)G$$

➔ **Constant rate of production**

However the initial value of the **gain current depends on d** (via the weighing field)

$$di_{gain} \propto dN_{Gain} q v_{sat} (\frac{k}{d})$$

➔ **Gain current ~ 1/d**

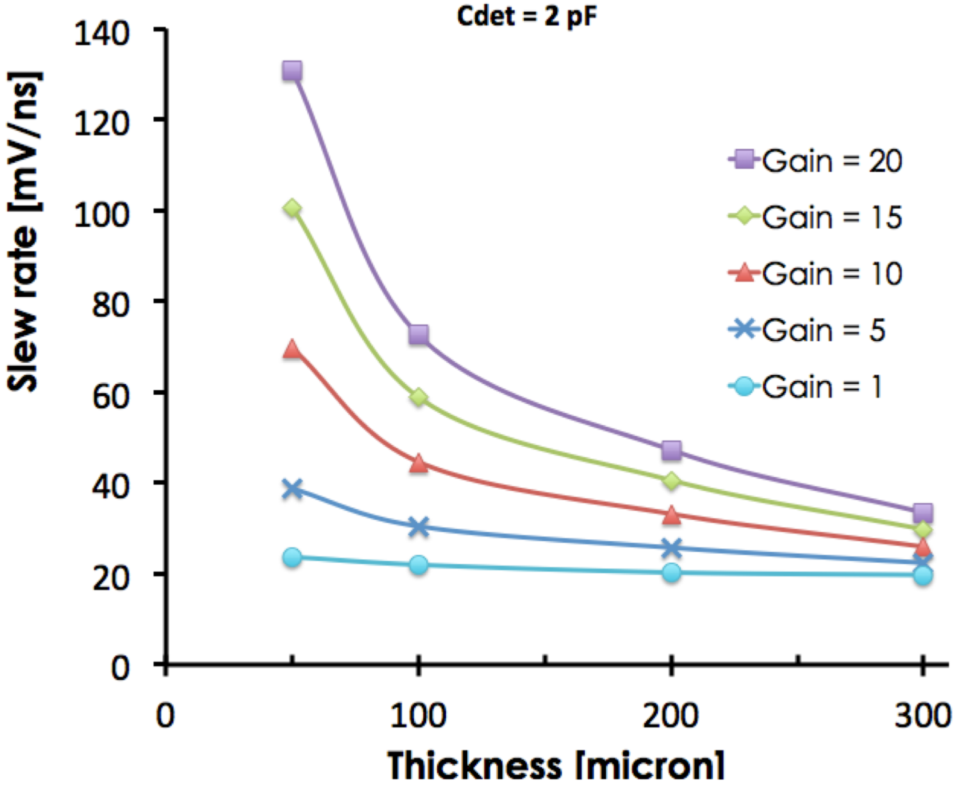
A given value of gain has much more effect on thin detectors

Gain current vs Initial current

$$\frac{di_{gain}}{i} \propto \frac{dN_{Gain}\,q v_{sat}\,\frac{k}{d}}{k q v_{sat}} = \frac{75(v_{sat}dt)\,G q v_{sat}\,\frac{k}{d}}{k q v_{sat}} \propto \boxed{\frac{G}{d}}\,dt$$

!!!

➔ Go thin!!



(Real life is a bit more complicated, but the conclusions are the same)

Full simulation

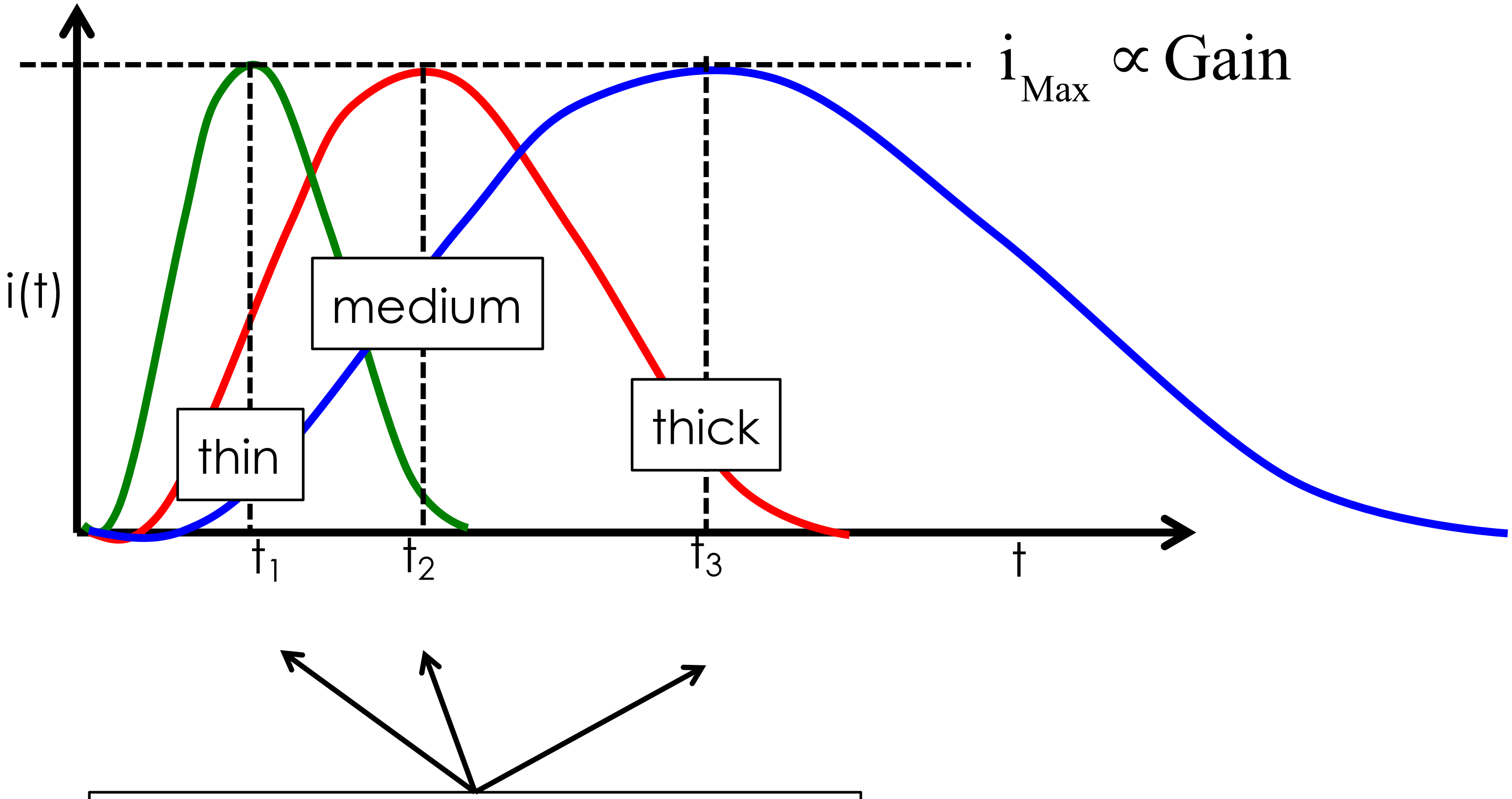
(assuming 2 pF detector capacitance)

300 micron:
~ 2-3 improvement
with gain = 20

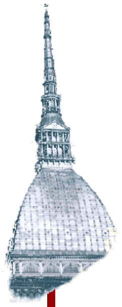
Significant improvements in time resolution require thin detectors

Gain and Maximum current

$$\frac{dV}{dt} \propto \frac{G}{d}$$



The rise time depends only on the sensor thickness ~ 1/d



Ultra Fast Silicon Detectors

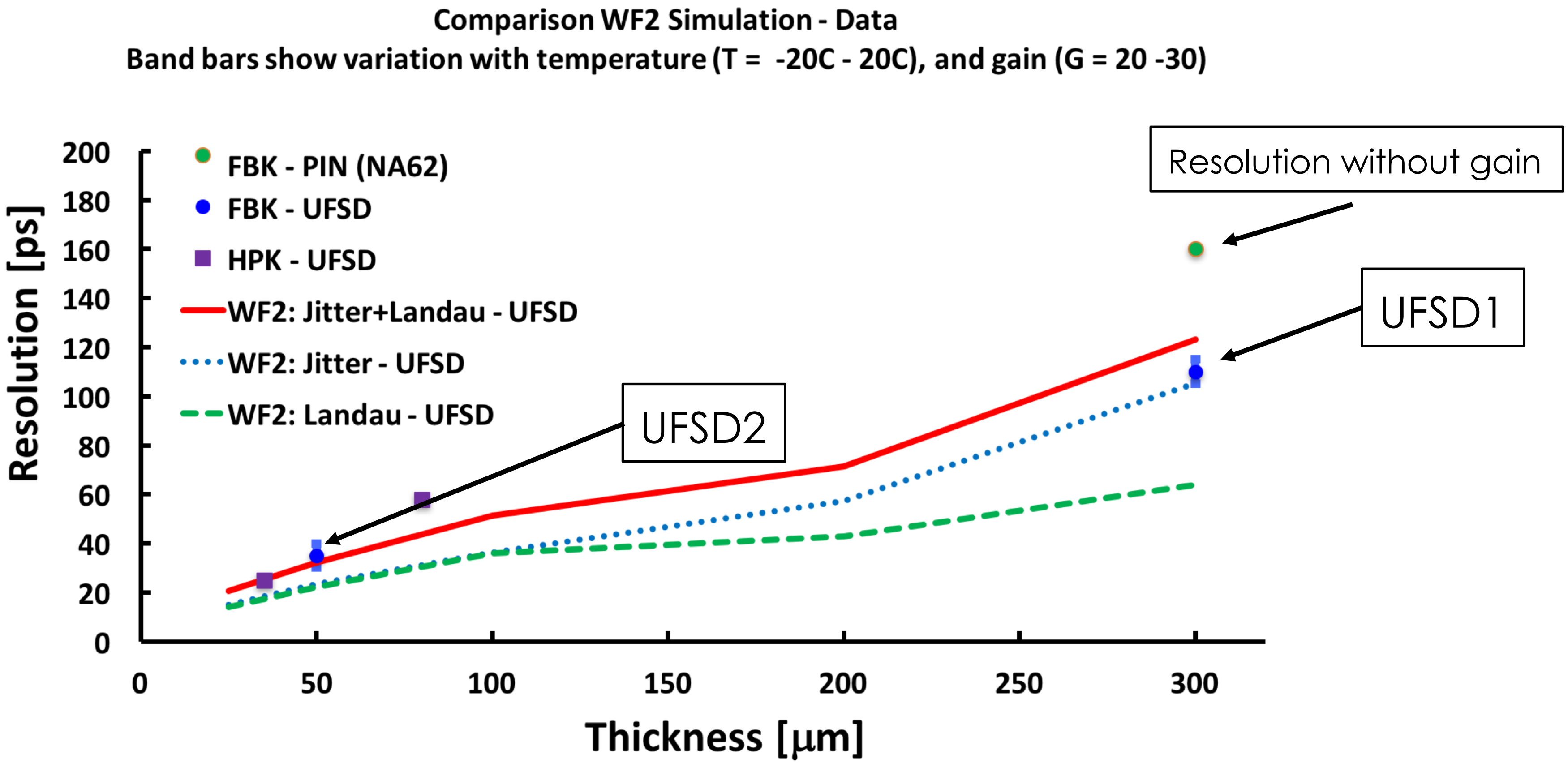
UFSD are LGAD detectors optimized to achieve the best possible time resolution

Specifically:

1. Thin to maximize the slew rate (dV/dt)
2. Parallel plate – like geometries (pixels..) for most uniform weighting field
3. High electric field to maximize the drift velocity
4. Highest possible resistivity to have uniform E field
5. Small size to keep the capacitance low
6. Small volumes to keep the leakage current low (shot noise)

UFSD time resolution summary

UFSD achieved 30 ps time resolution



Comparison WF2 Simulation - Data

Band bars show variation with temperature (T = -20C - 20C), and gain (G = 20 -30)

Resolution without gain

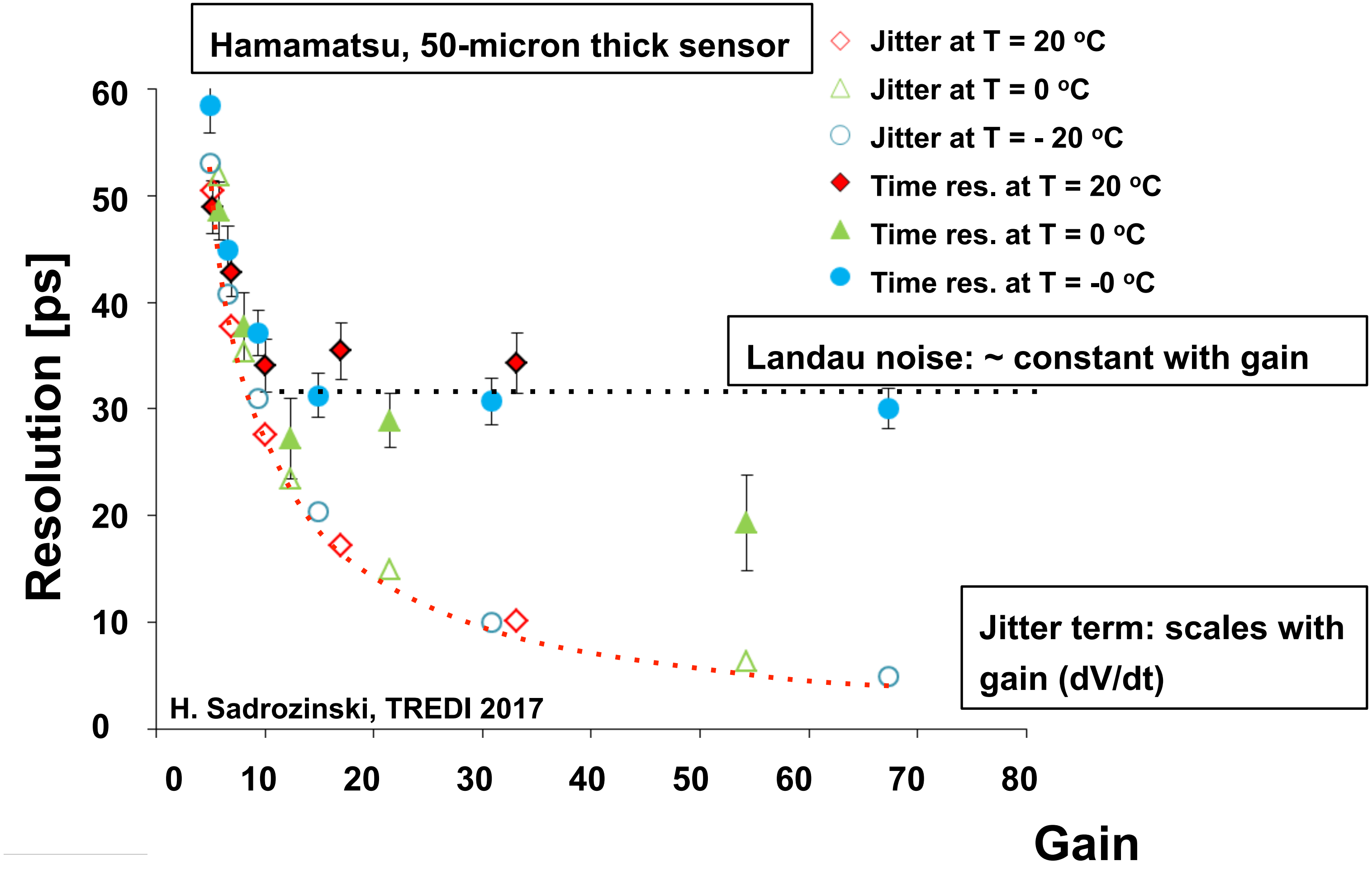
UFSD1

UFSD2

UFSD: HPK time resolution

UFSD from Hamamatsu: 30 ps time resolution,

Value of gain ~ 20



Hamamatsu, 50-micron thick sensor

Landau noise: ~ constant with gain

Jitter term: scales with gain (dV/dt)

H. Sadrozinski, TREDI 2017

Irradiation effects

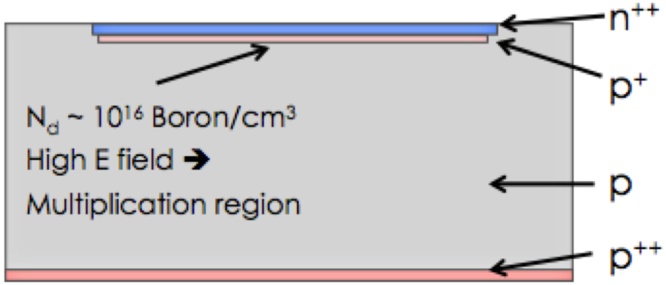
Irradiation causes 3 main effects:

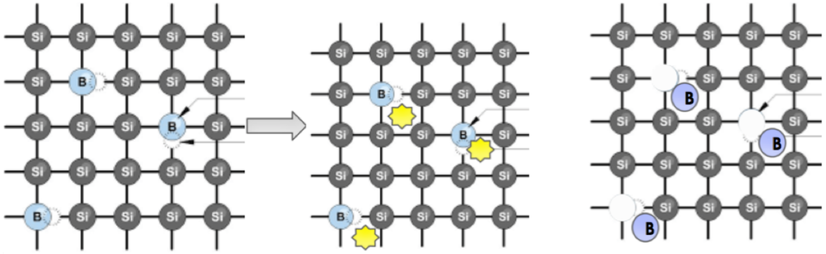
- Decrease of charge collection efficiency due to trapping
  - ➔ Very small in thin sensor
- Increased leakage current, shot noise ➔ back up slides
- Gain layer disappearance ➔ following slides

Gain layer de-activation

Unfortunate fact: irradiation de-activate p-doping removing Boron from the reticle

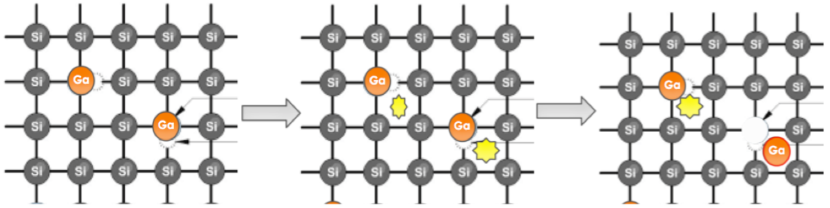
$$N(\emptyset) = N(0) * e^{-c\emptyset}$$



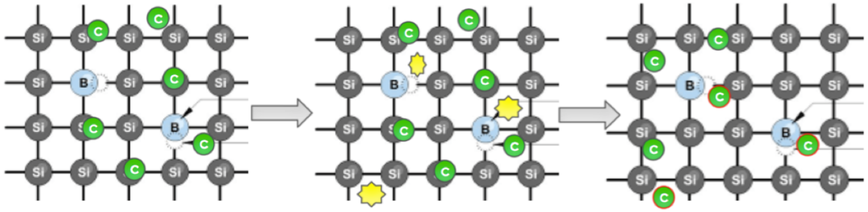


Boron
Radiation creates interstitial defects that inactivate the Boron: Si_i + B_s ➔ Si_s + B_i

Two possible solutions: 1) use Gallium, 2) Add Carbon

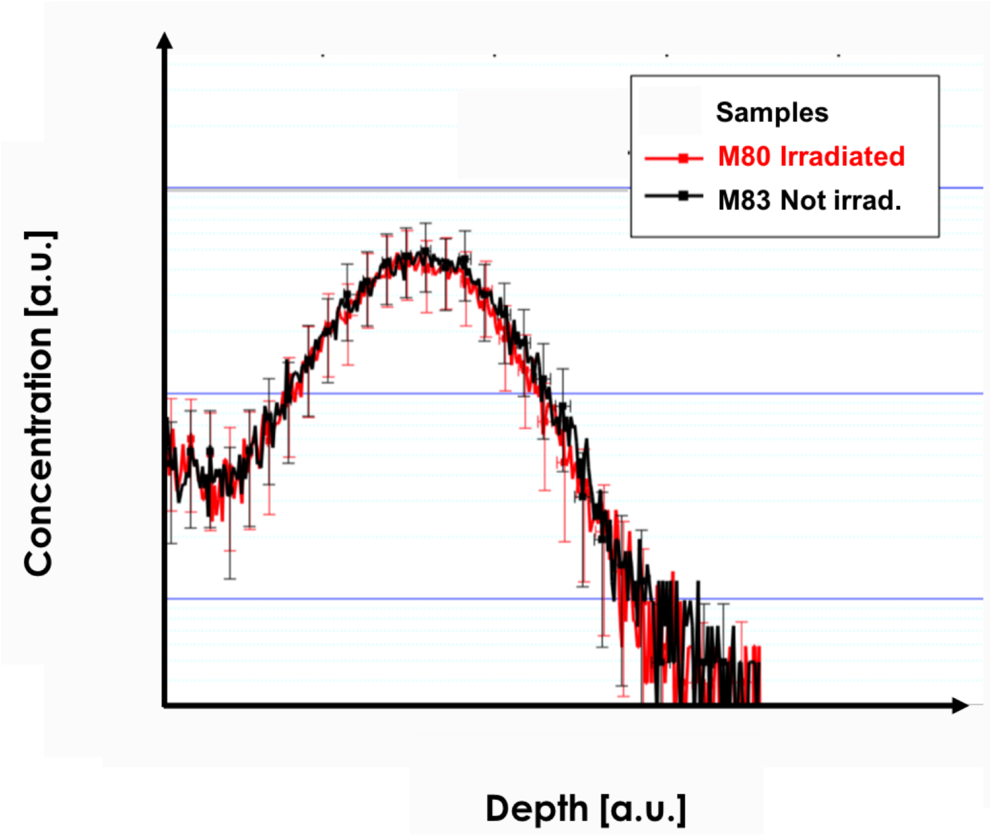


Gallium
From literature, Gallium has a lower possibility to become interstitial



Carbon
Interstitial defects filled with Carbon instead of with Boron and Gallium

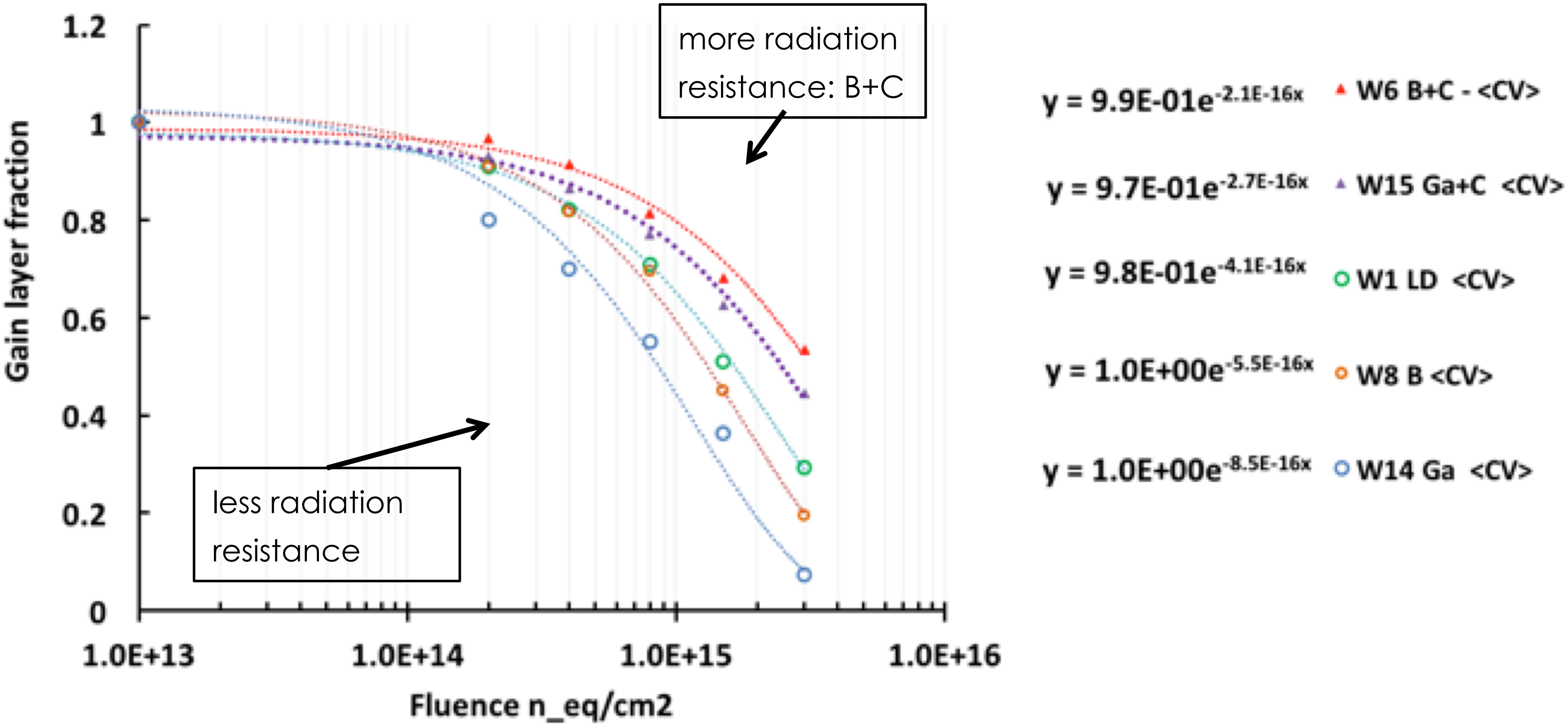
Is the Boron still there?



Yes, **the Boron is still there**, but it is not active any more…

Instead of being "substitutional" (i.e. in the place of a Silicon atom) **is "interstitial"** (i.e. In the middle of the lattice, not electrically active)

UFSD2: studio della resistenza alle radiazioni



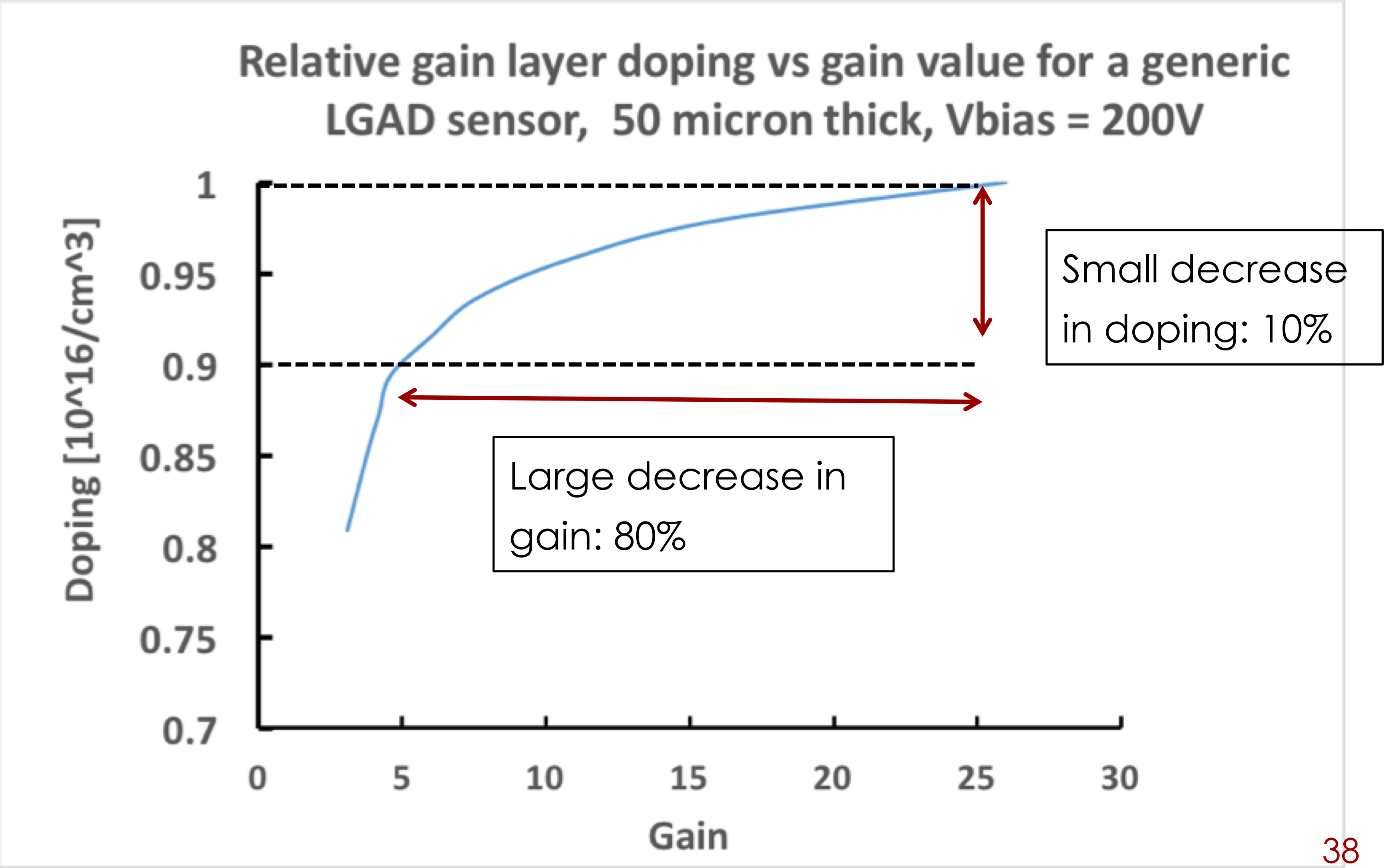
more radiation resistance: B+C

less radiation resistance

1) Gallium is actually is less rad-hard than Boron
2) Carbon addition works really well, increasing by a factor of 2 the radiation hardness

Gain vs gain layer doping

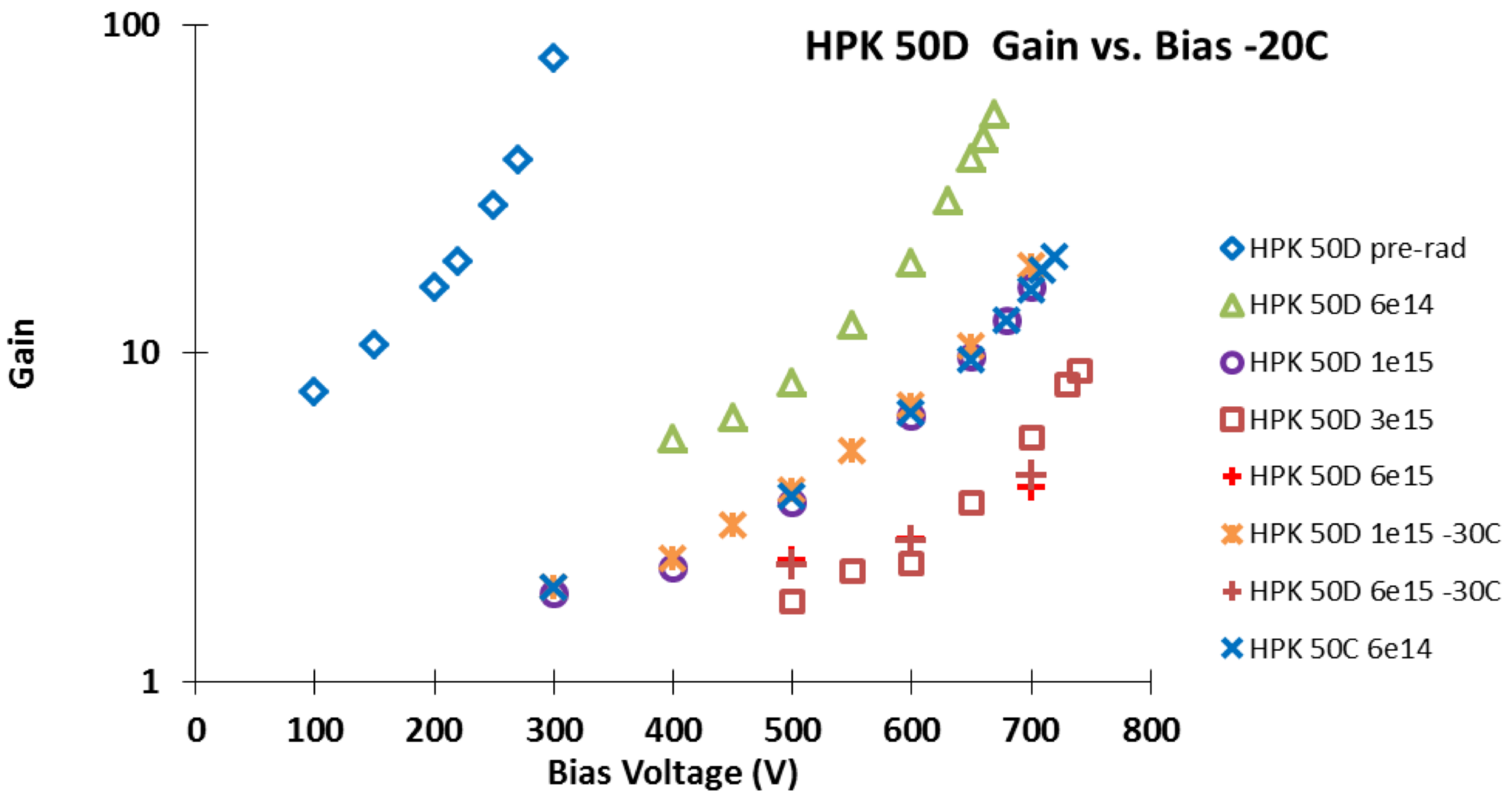
Unfortunately, the gain is very sensitive to the doping level



Small decrease in doping: 10%

Large decrease in gain: 80%

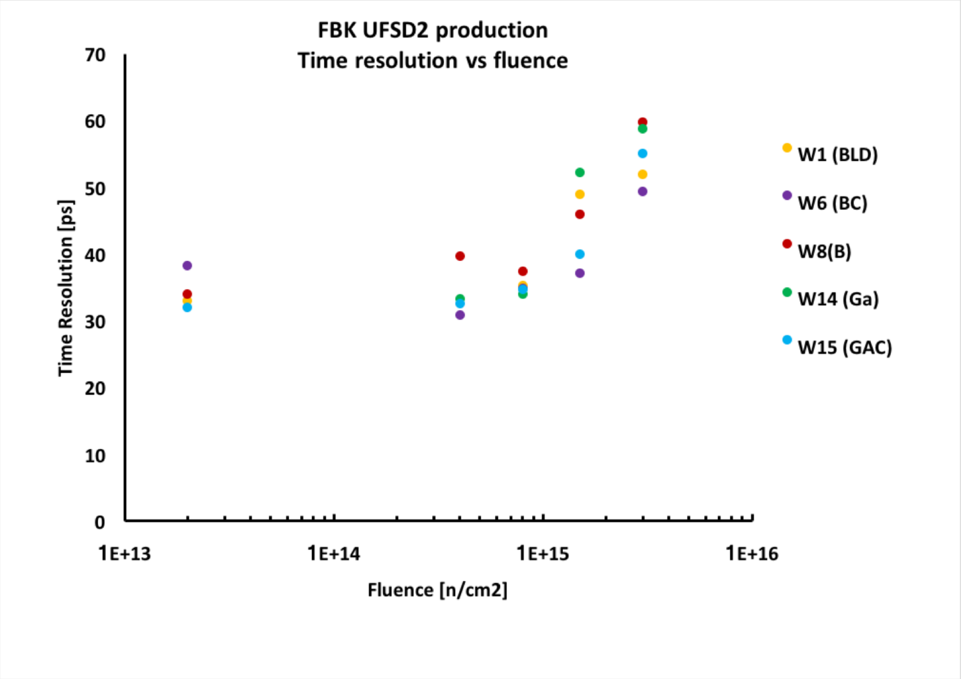
Gain in irradiated sensors

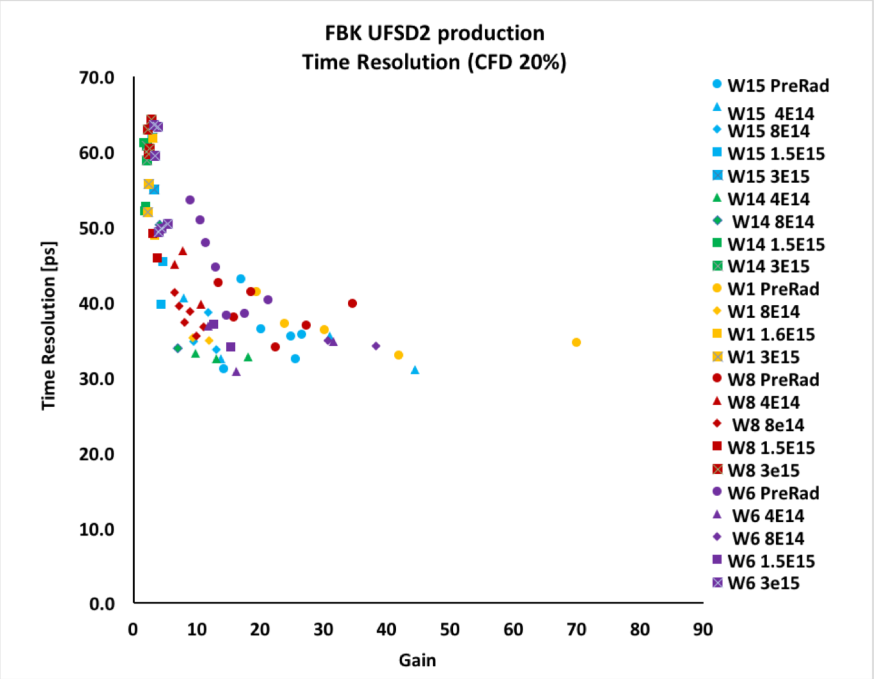


the gain layer disappearance is compensated by external bias

UFSD: Time resolution after irradiation

FBK production of UFSD sensors: time resolution for different fluence





Very complex irradiation campaign, lot's of samples and fluences

Achieved:

- **Unchanged time resolution of ~ 35 ps, up to ~ 2E15 n/cm2**
- **Time resolution of 50 ps up to 3E15 n/cm2**

Why noise in LGAD does not degrade time resolution?

Time resolution in LGAD is determined by jitter and charge non uniformity:

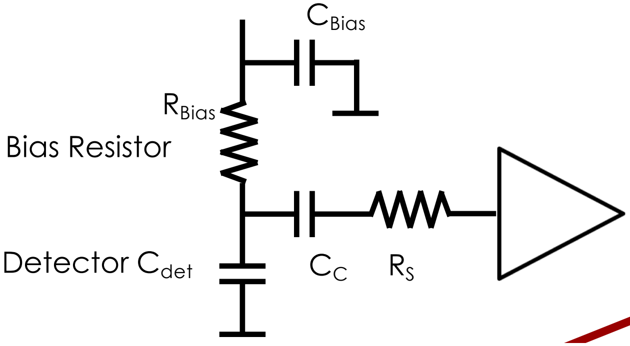
$$\sigma_t^2 = \left(\frac{N}{dV/dt}\right)^2 + \sigma_{Landau\ Noise}^2$$

The jitter term contains electronic noise and shot noise:

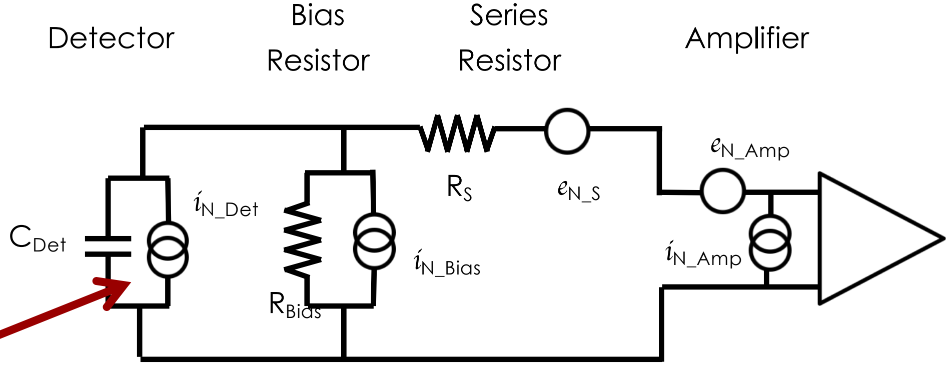
$$\textbf{Jitter} = \frac{\sqrt{N_{el}^2 + N_{Shot\ Noise}^2}}{dV/dt}$$

Noise Aide memoire

Real life



Noise Model



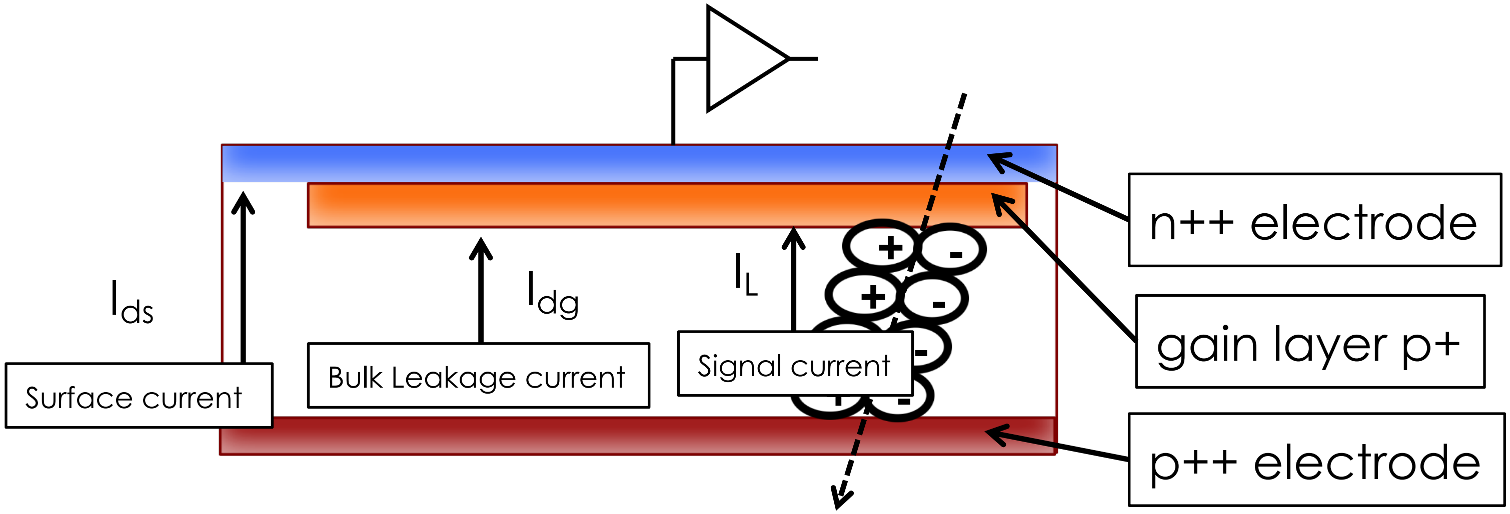
Only a part of this term, the detector current shot noise, depends on the gain

$$Q_n^2=(2eI_{Det})A_i\tau+\left(\frac{4kT}{R_{Bias}}+i^2_{N\_Amp}\right)A_i\tau+\underbrace{(4k\tau R_s+e^2_{N\_Amp})A_v\frac{C^2_{Det}}{\tau}}_{\frac{Q^2_{n0}}{\tau}}+A_{vf}A_fC^2_{Det}$$

Keeping only the most important terms and setting $A_i = 1$

Let's explore the shot noise…

Shot noise in LGAD - APD



n++ electrode

gain layer p+

p++ electrode

I_{ds}

Surface current

I_{dg}

Bulk Leakage current

I_L

Signal current

$$i^2_{Shot} = 2eI_{Det} = 2e\left[I_{Surface} + (I_{Bulk} + I_{Signal})M^2F\right]$$

Correction factor to the standard Shot noise, due to the noise of the multiplication mechanism

$$F = Mk + \left(2 - \frac{1}{M}\right)(1-k)$$

$$F \sim M^x$$

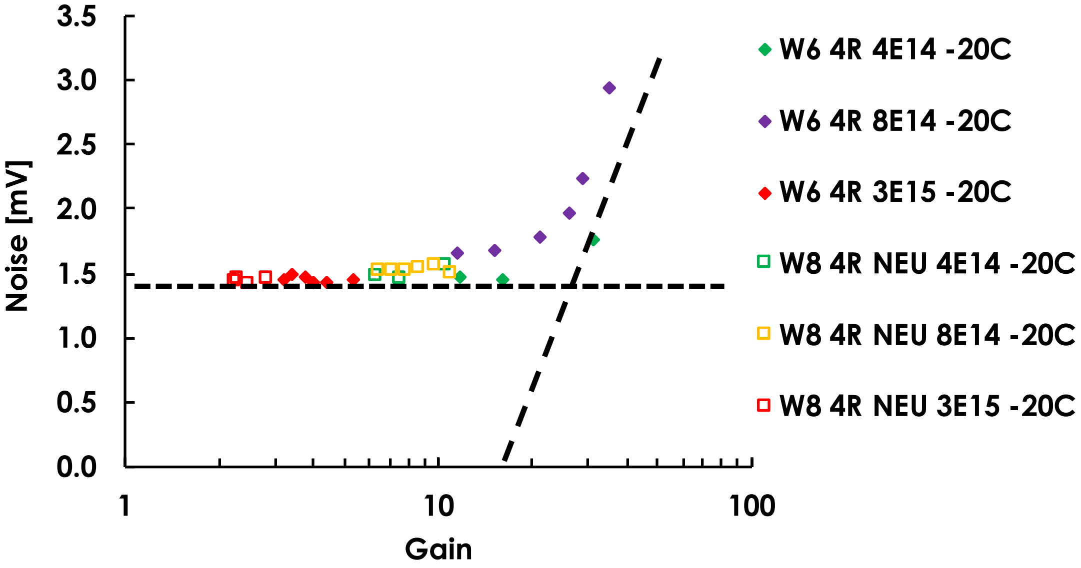
k = e/h ionization rate

x = excess noise index

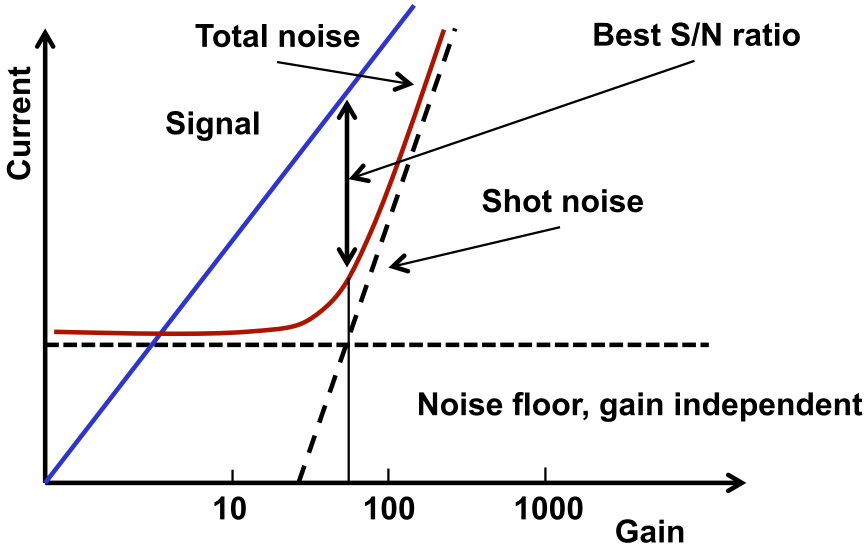
M = gain

$$F = \frac{\langle M^2 \rangle}{\langle M \rangle^2} \Rightarrow \langle M^2 \rangle = \langle M \rangle^2 F$$

Noise increase as a function of fluence and gain

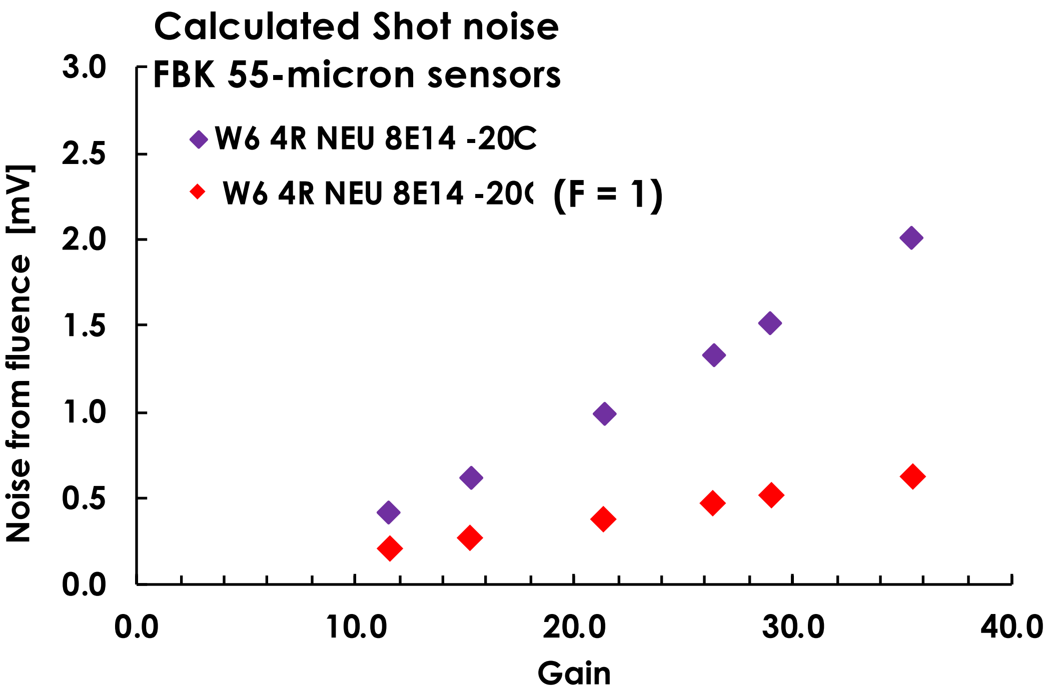


Data and model look similar.



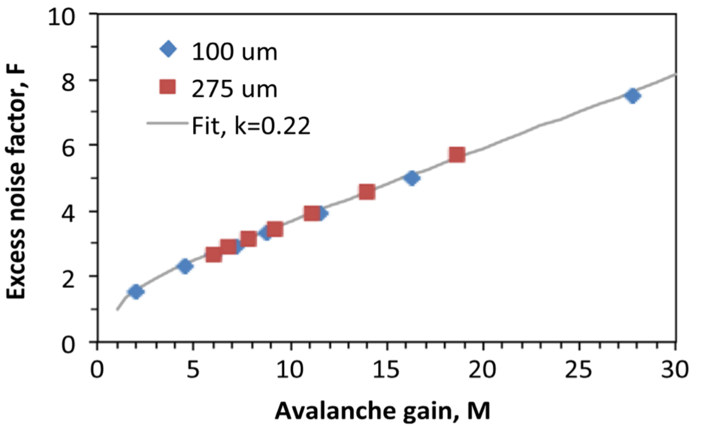
Goal: the noise from Silicon current should stay below that of the electronics

The role of the excess noise factor



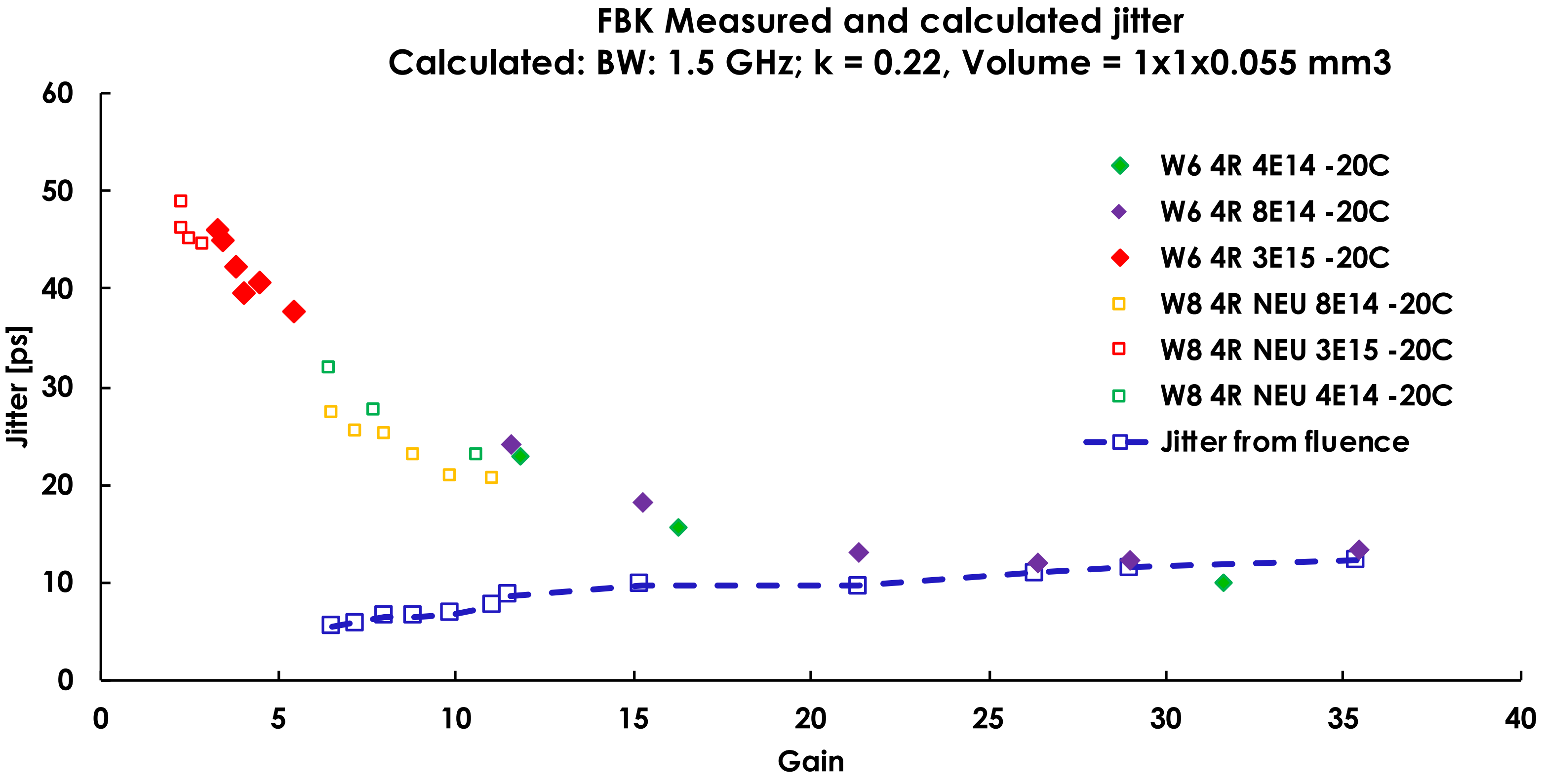
Excess noise factor: noise of the multiplication process

$$F = Gk + \left(2 - \frac{1}{G}\right) * (1 - k)$$



Shot noise is actually dominated by the excess noise factor: at gain = 20 the excess noise factor more than doubles the shot noise without it

Shot noise and Jitter



The Jitter, instead of decreasing, is becoming constant due to the contribution of the shot noise.

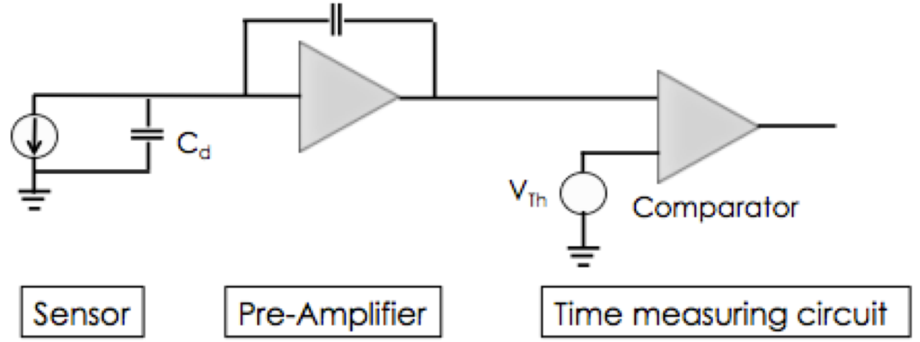
Why noise is not a problem yet?

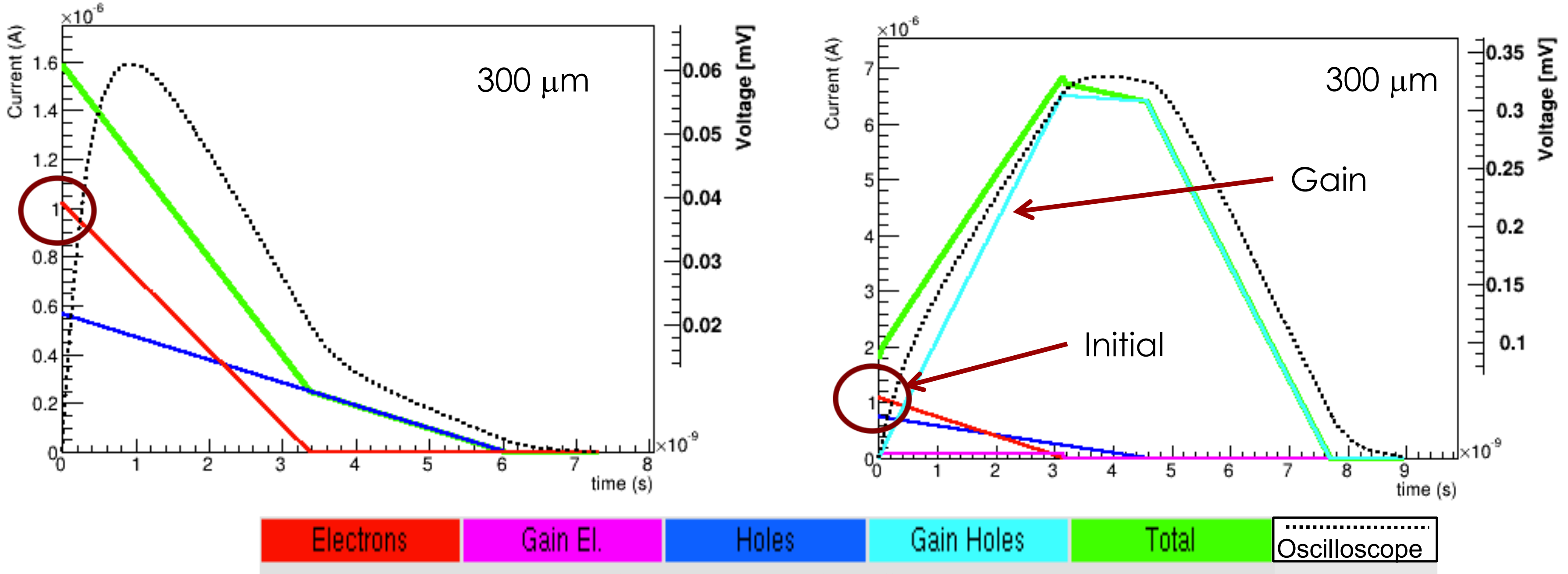
- Noise increase is driven by bulk current shot noise
- The calculated noise values are within 20% of the measured values
- The shot noise is large only when the gain and the bulk leakage current are high ➔ not very common
- After irradiation, the gain decreases, and as a unintended consequence, the shot noise stays small.
- The values of shot noise are below the Landau noise

Electronics

To fully exploit UFSDs, dedicated electronics needs to be designed.

The signal from UFSDs is different from that of traditional sensors





Simulated Weightfield2

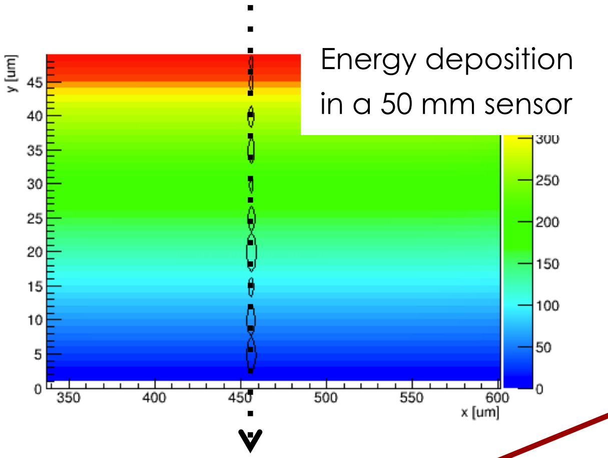
Pads with no gain

Charges generated uniquely by the incident particle

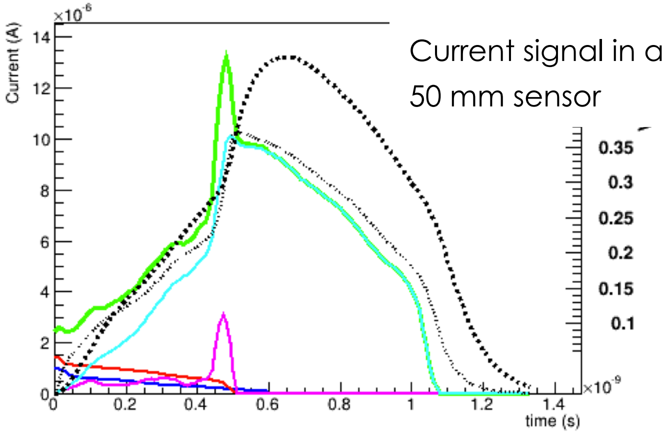
Pads with gain

Current due to gain holes creates a longer and higher signal

Electronics: What is the best pre-amp choice?

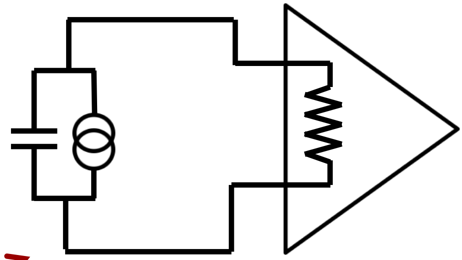


Energy deposition in a 50 mm sensor

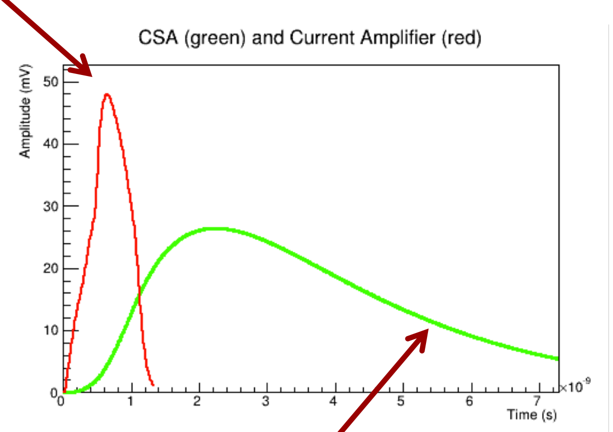


Current signal in a 50 mm sensor

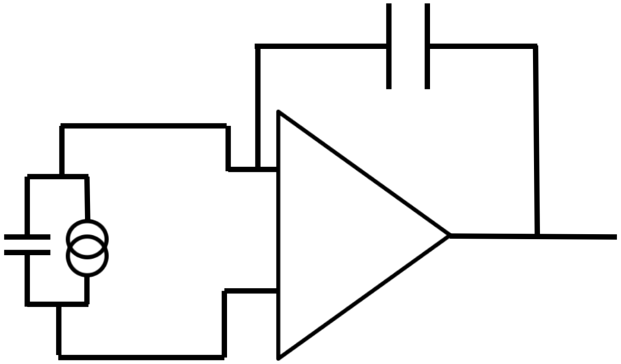
Current Amplifier



- Fast slew rate
- Higher noise
- Sensitive to Landau bumps



Charge Sensitive Amplifier



- Slower slew rate
- Quieter
- Integration helps the signal smoothing

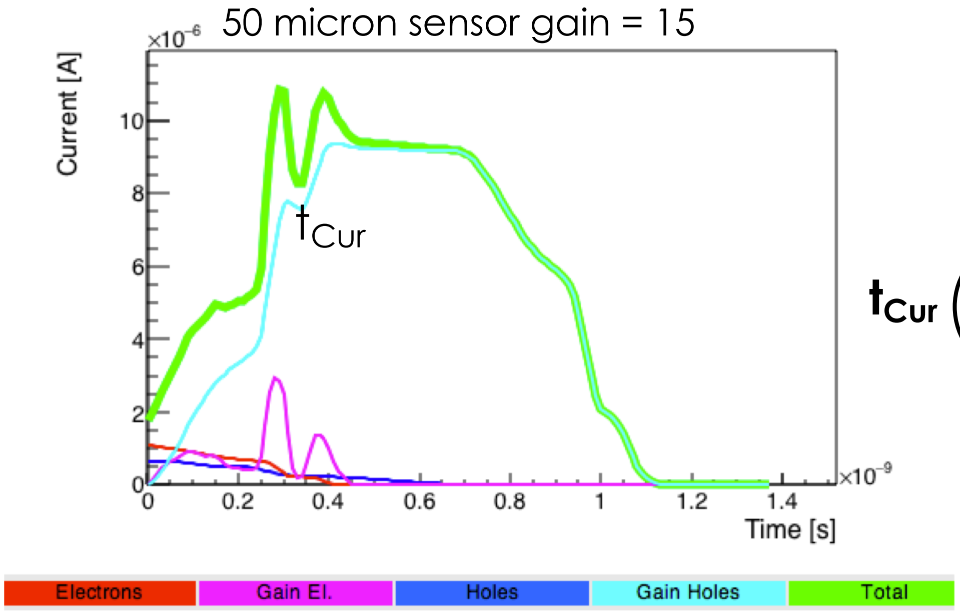
The players: signal, noise and slope

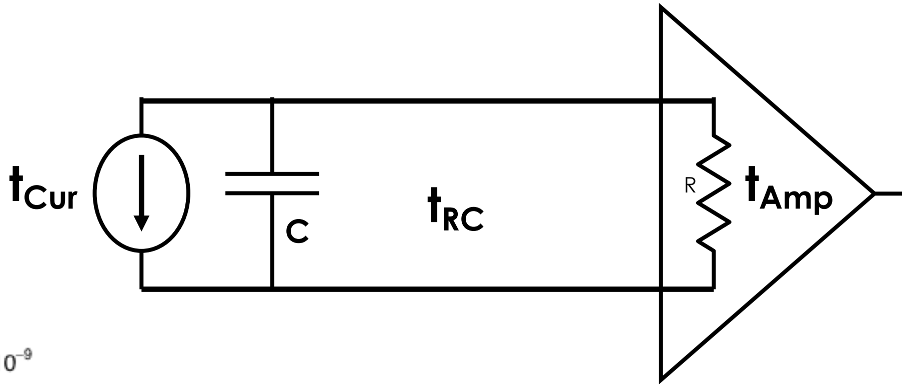
Signal dV/dt

Landau Noise

Shot Noise

Electronic Noise





The current rise time (t_{Cur})

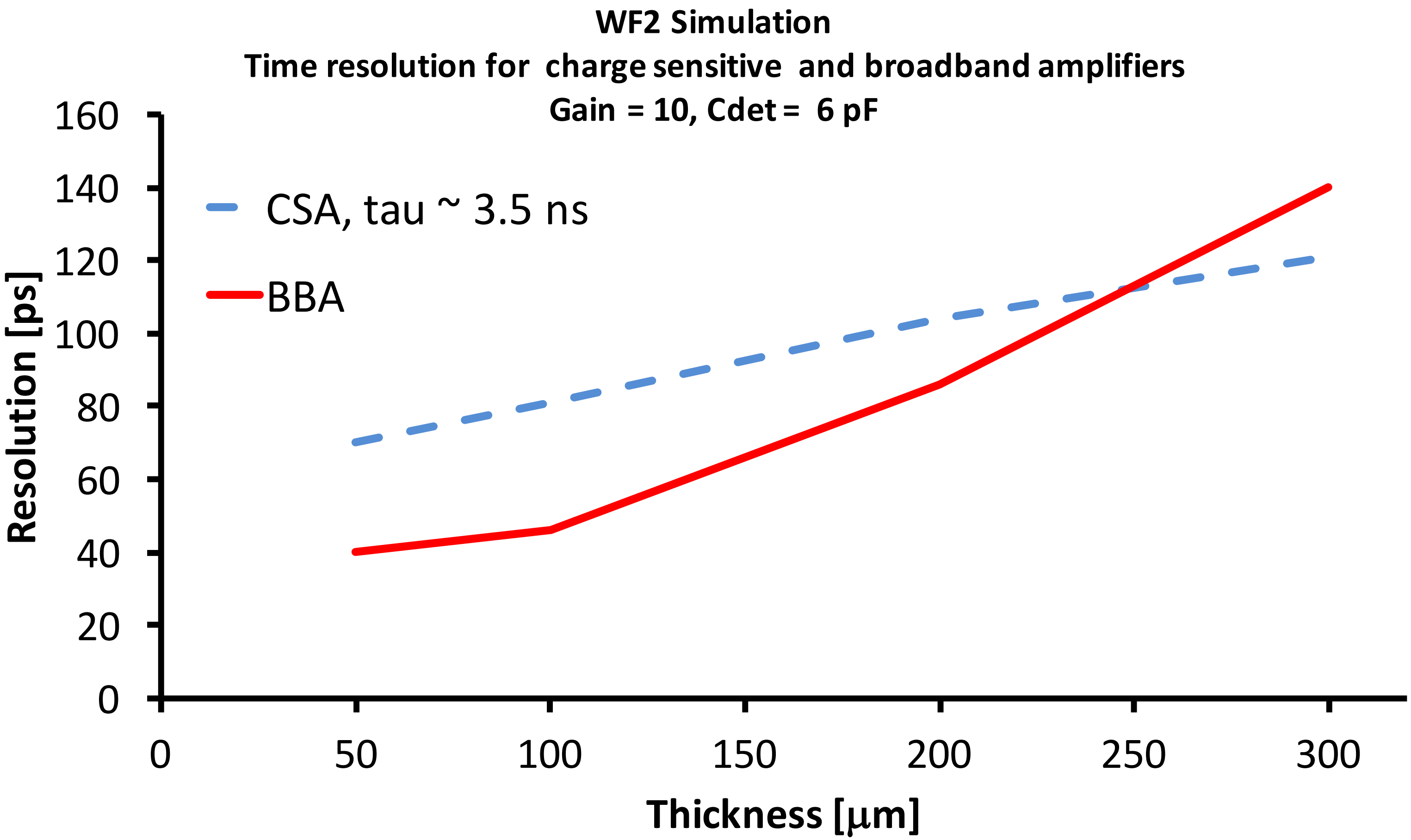
The RC circuit (t_{RC})

Amplifier rise time (t_{Amp})

There are 3 quantities determining the output rise time after the amplifier:

1. The signal rise time (t_{Cur})
2. The RC circuit formed by the detector capacitance and the amplifier input impedance (t_{RC})
3. The amplifier rise time (t_{Amp})

Integrator or current amplifier?



- integrators work best with signals that are of the same length of their integration time
- Current amplifiers work best with very fast signals

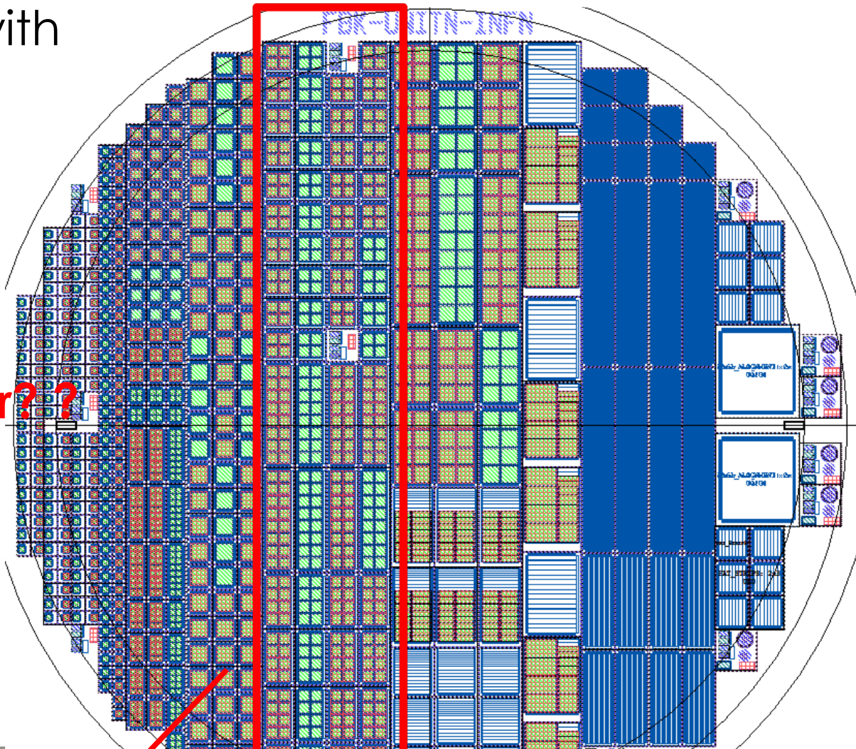
From one pad to a tracker

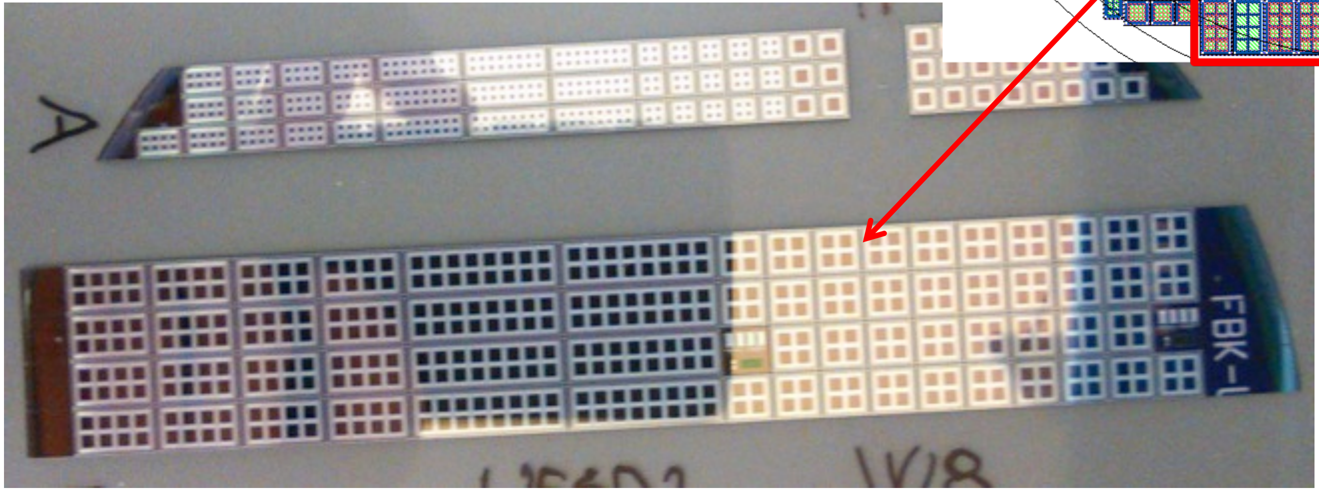
We have produced thousands of UFSDs, with many shapes, thicknesses, gains etc..

We know very well how a single pads and small array work, however….

Are we able to produce a full large tracker? ?

- **Uniformity**
- **Fill factor**



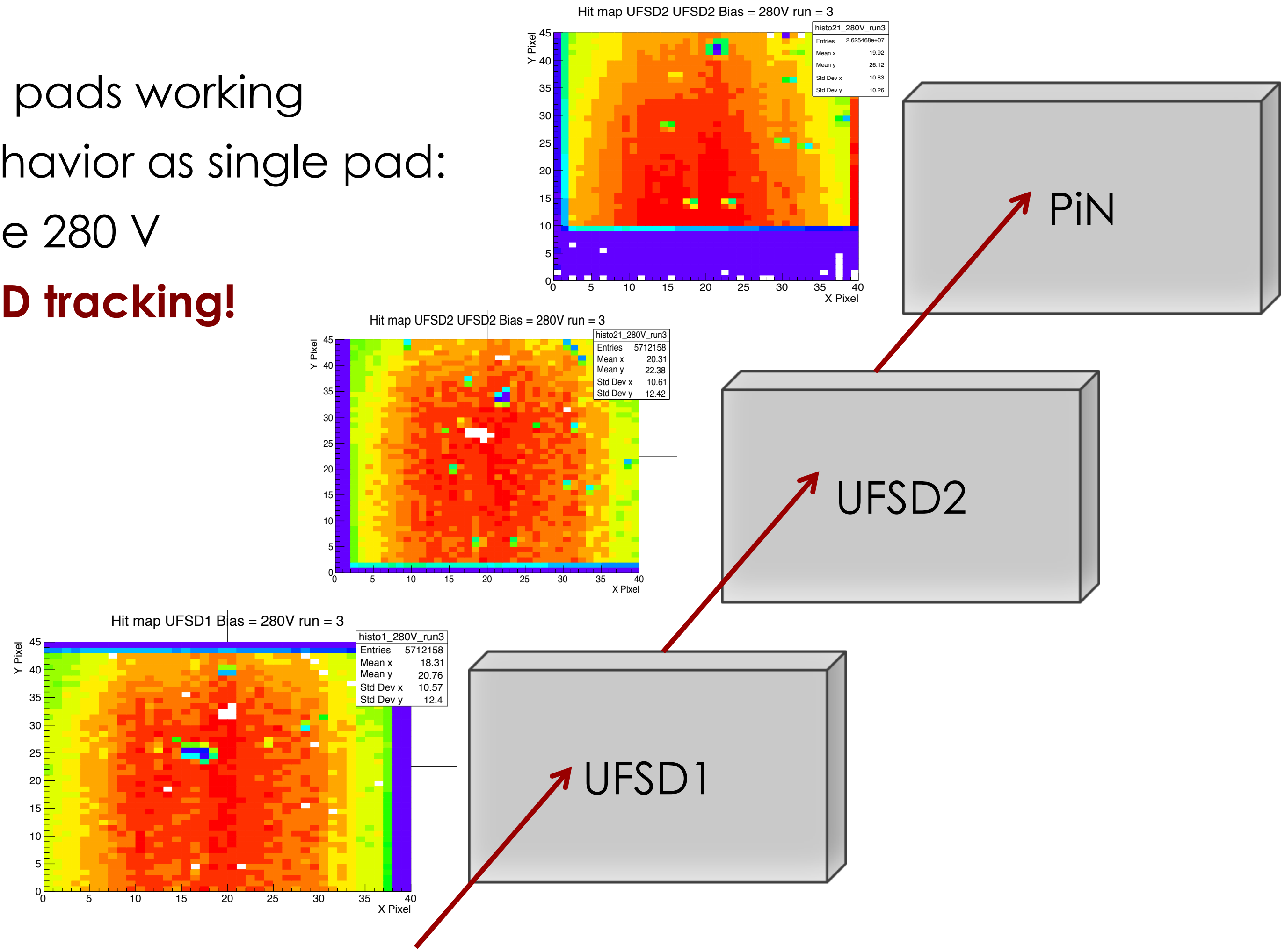


Multi-pad sensors: TDCpix & FBK-UFSD

Bump-bonded NA62 TDCpix ROC to FBK-UFSD sensor

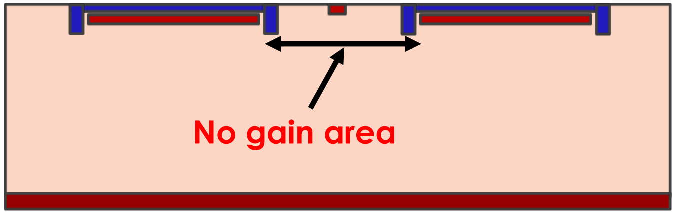
NA62 ROC: 40x45 pads, each 300x300 μm^2 (1800 pads)

- More than 99% of pads working
- Same voltage behavior as single pad: breakdown above 280 V
- **First example of 4D tracking!**



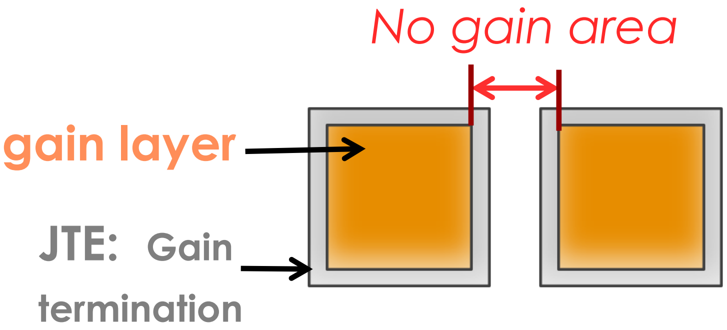
Fill factor

The fill factor is mainly determined by the inactive gap between sensors.



Current measured gap size:

- ~ 70 micron for CNM
- ~ 100 micron for HPK
- ~ 70 micron for FBK



This gap affects directly the detector acceptance as we have only one layer: a 70 micron gap corresponds to a 91% fill factor

Goal: 30 micron gap = 96% fill factor

Currently under study, looks possible…

Fill factor: optimization of current design

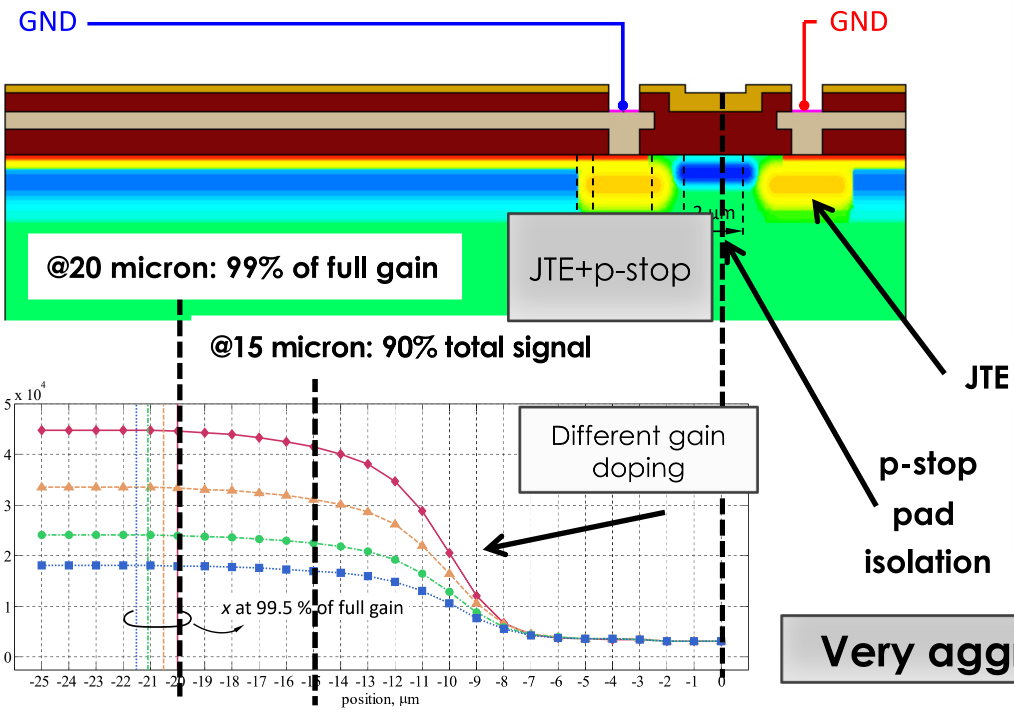
The gap is due to **two components**:

1) Adjacent gain layers need to be isolated (**JTE & p-stop**)

2) Bending of the E field lines in the region around the JTE area

Both under optimization Different junction termination/p-stop design

- **CMS Goal: 30 micron gap = 96% fill factor**



@20 micron: 99% of full gain

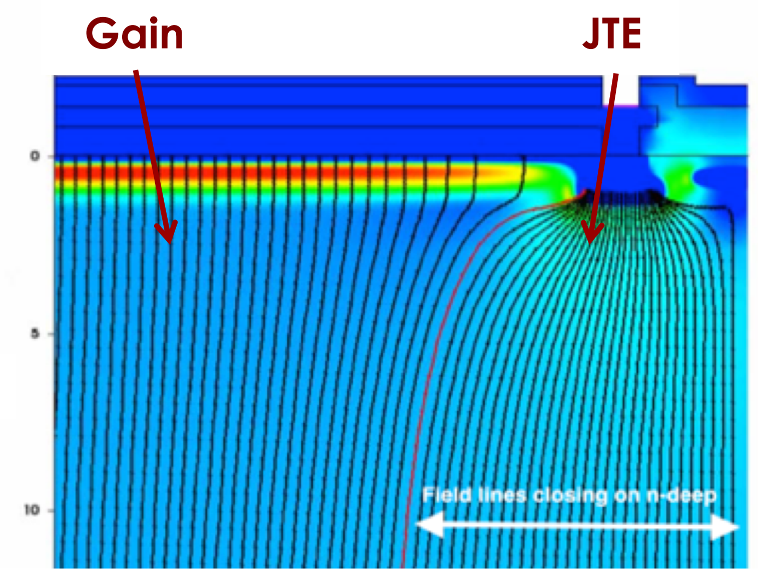
JTE+p-stop

@15 micron: 90% total signal

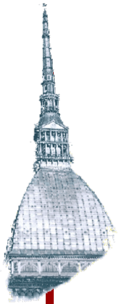
Different gain doping

JTE

p-stop pad isolation



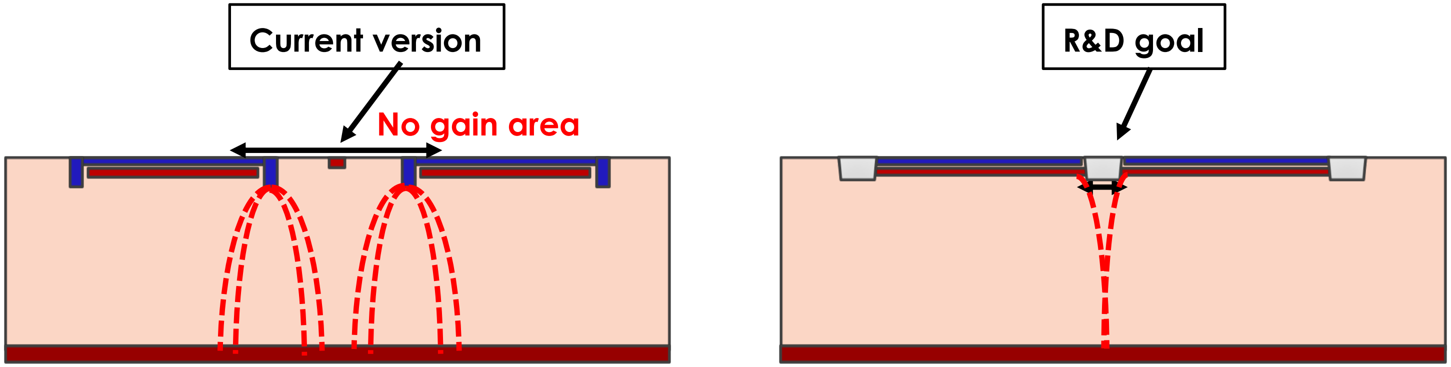
Very aggressive design: <10 micron per side



Fill factor solution 1: trenches

Trenches (the same technique used in SiPM):

- No pstop,
- No JTE ➔ no extra electrode bending the field lines



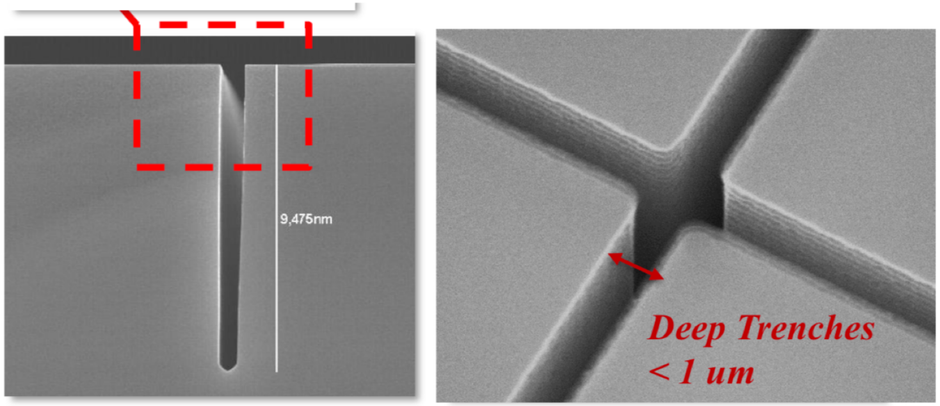
JTE + p-stop design

Trench design

Trench isolation technology

- Typical trench width < 1 um
- Max Aspect ratio: 1:20
- Trench filling with: SiO_2, Si_3N_4, PolySi

CMM
CENTRE FOR MATERIALS AND MICROSYSTEMS

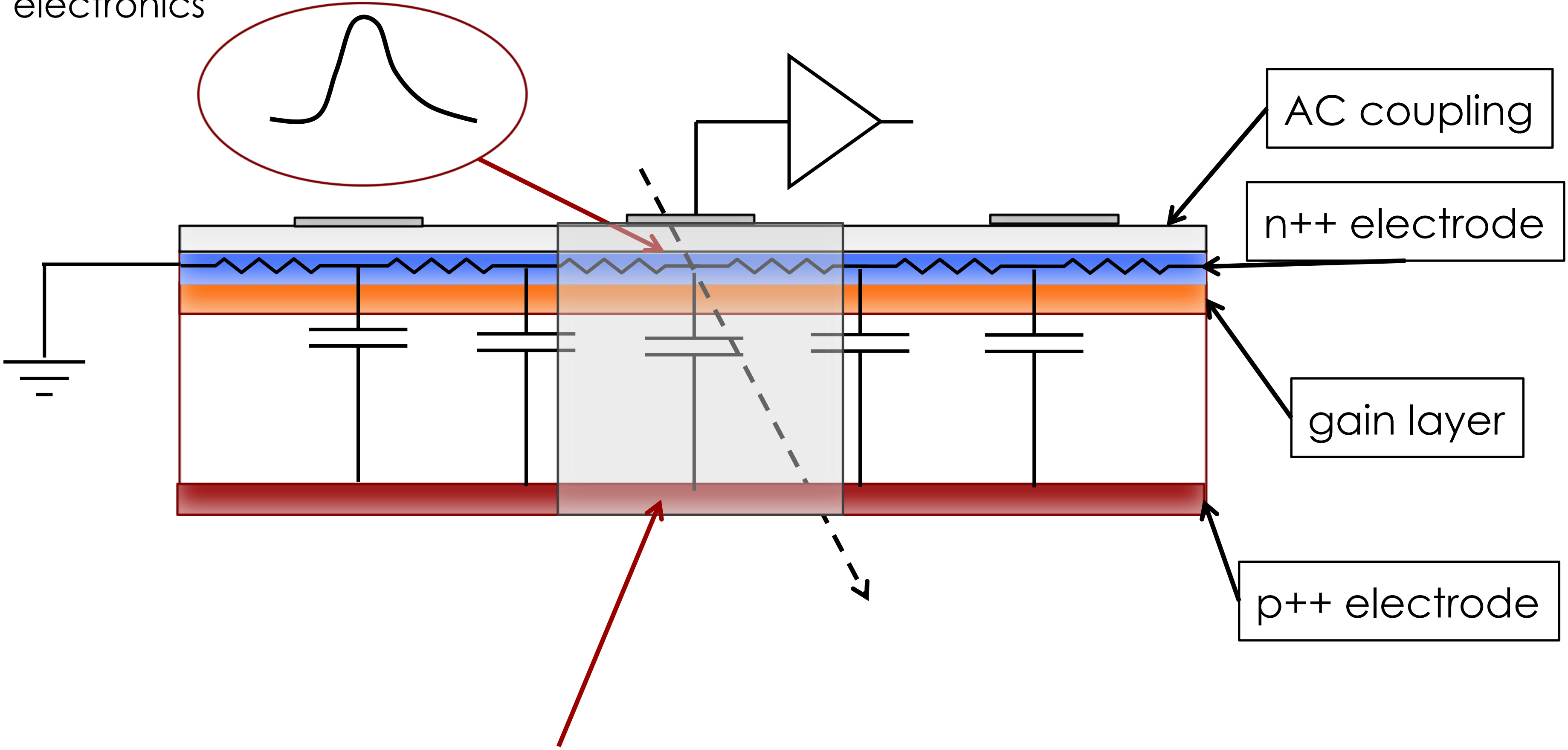


Fill factor solution 2: Resistive electrode

The signal is frozen on the resistive sheet, and it's AC coupled to the electronics

➔ 100% fill factor

➔Segmentation is achieved via AC coupling



The AC read-out sees only a small part of the sensor:

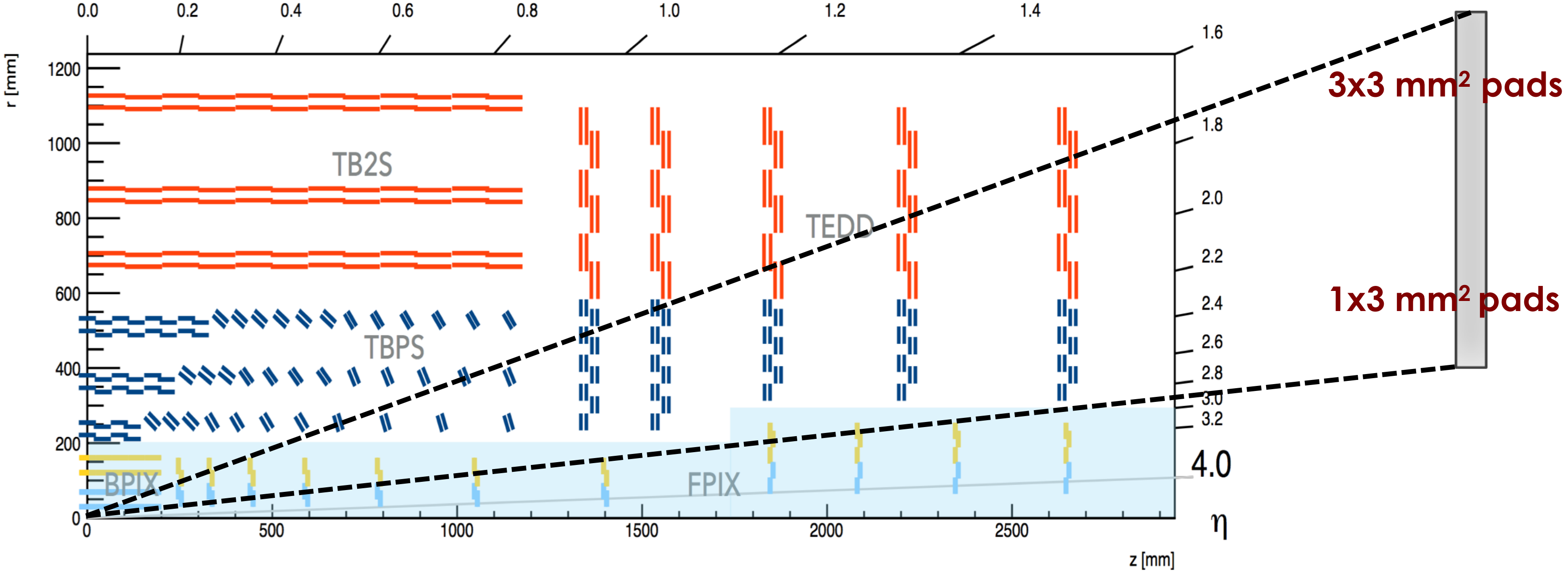
small capacitance and small leakage current.

And now we need to build the detector..

CMS and ATLAS have now in their upgrade proposal the combined construction of ~ 20 m2 of UFSD sensors.

Main challenges:

- Sensor: moving from one pad to large area
- Electronics: need to design an appropriate chip

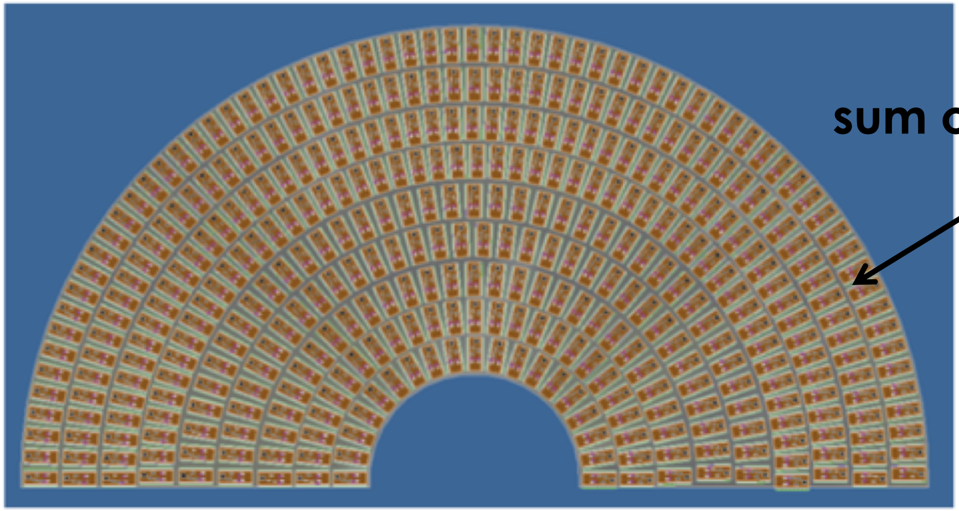


And: backend electronics, mechanics, cooling, HV & LV distribution, High precision clock, data transmission

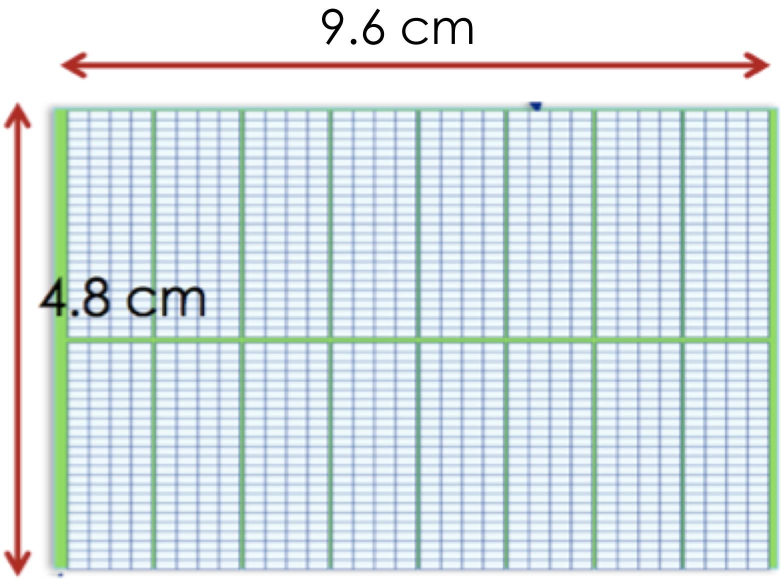
ETL: Endcap Timing Layer

The chosen sensors for ETL are UFSD

one layer
per side,
each made of
two disks



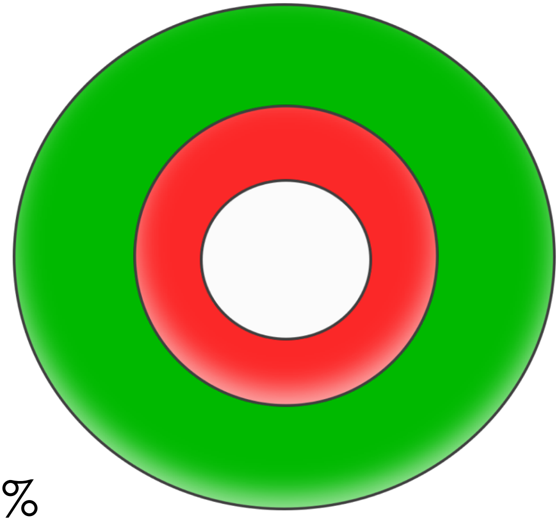
- ~ 1800 sensors:
- 4.8 x 9.6 cm^2 --- Large Sensors
- Thickness of active area: 40-50 microns
- Pad size: 1 x 3 mm^2 (1536 pads)



SENSORS: state of the art

UFSD: 35 ps resolution for fluences up to **5 - 6e14 neq/cm²**

State-of-the-art sensors guarantee 80% of the ETL coverage

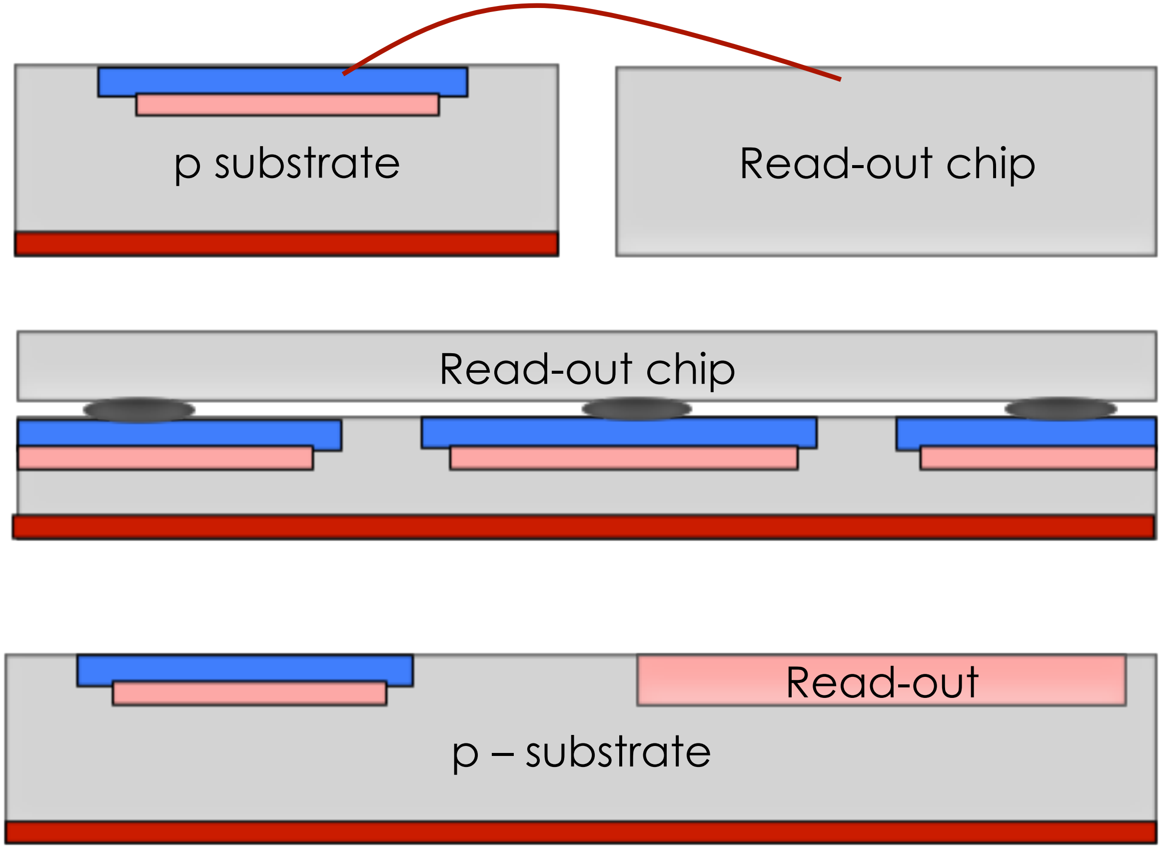


Low radiation : radius 55 – 110 cm ~2.8 m2 , ~80%
High radiation: radius 25 – 55 cm ~0.7 m2, ~20%

There are several options to cover the additional 20%

- R&D will demonstrate new solutions → next 18 months
- Allow degradation of resolution (~ 60 ps after 3000 fb-1)
- Have two layers

R&D: Can we use Monolithic technology?



Wire bonding

Bump bonding

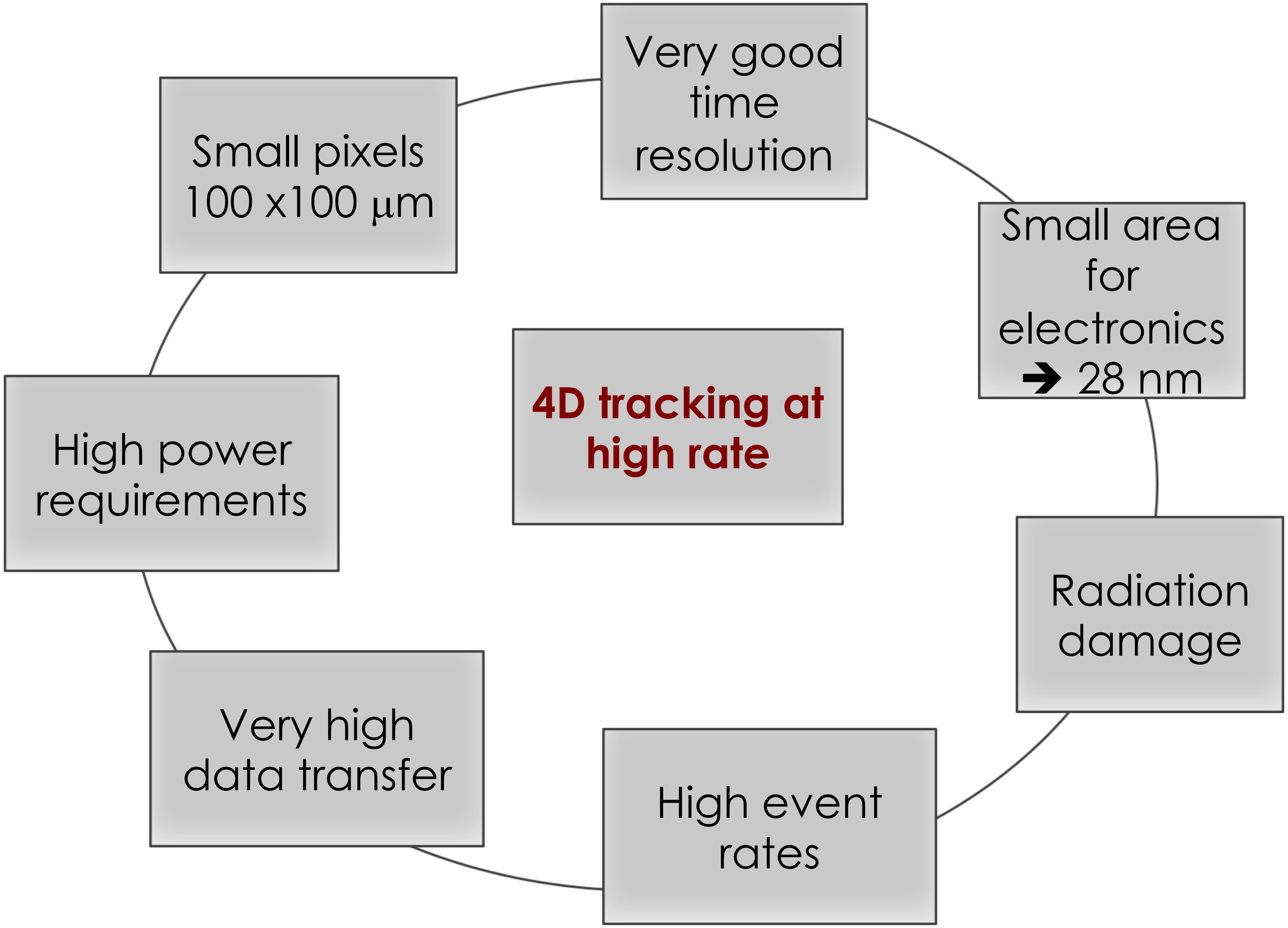
⇩

Monolithic

R&D in 5 years: space-time tracking at high rate

Imagine tracking with ~ 1000-2000 tracks @ 40 MHz crossing

This situation is the pinnacle of complications..



4D tracking at high rate

Very good time resolution

Small area for electronics ➔ 28 nm

Radiation damage

High event rates

Very high data transfer

High power requirements

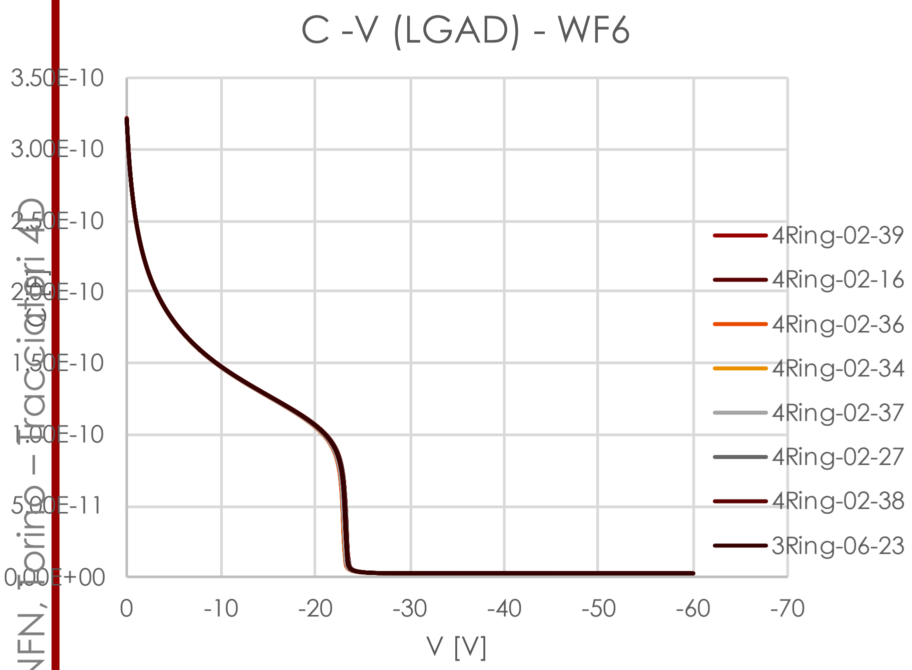
Small pixels 100 x100 μm

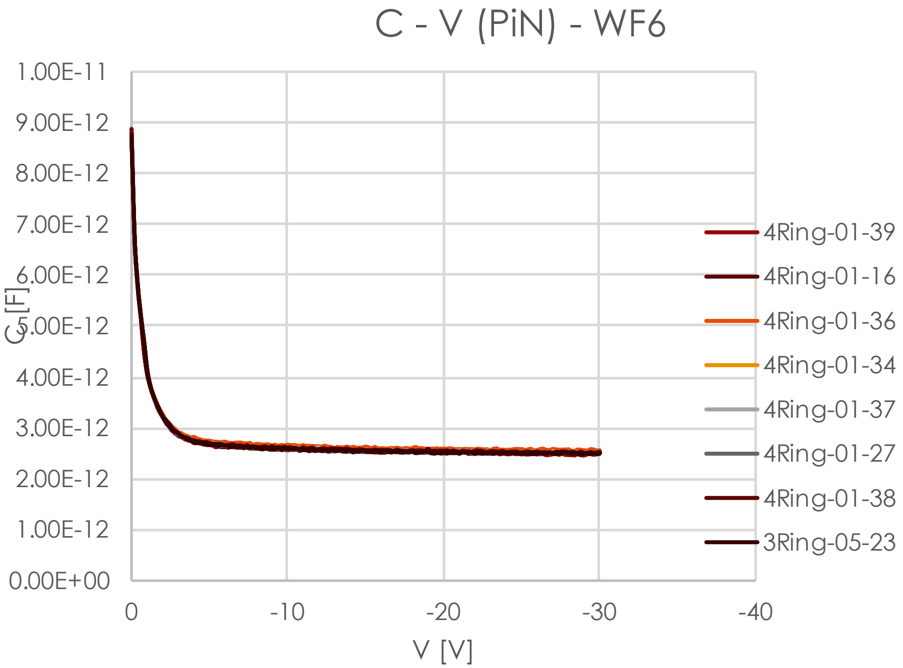
Laboratory measurements

What do you do in a lab to characterize an LGAD?

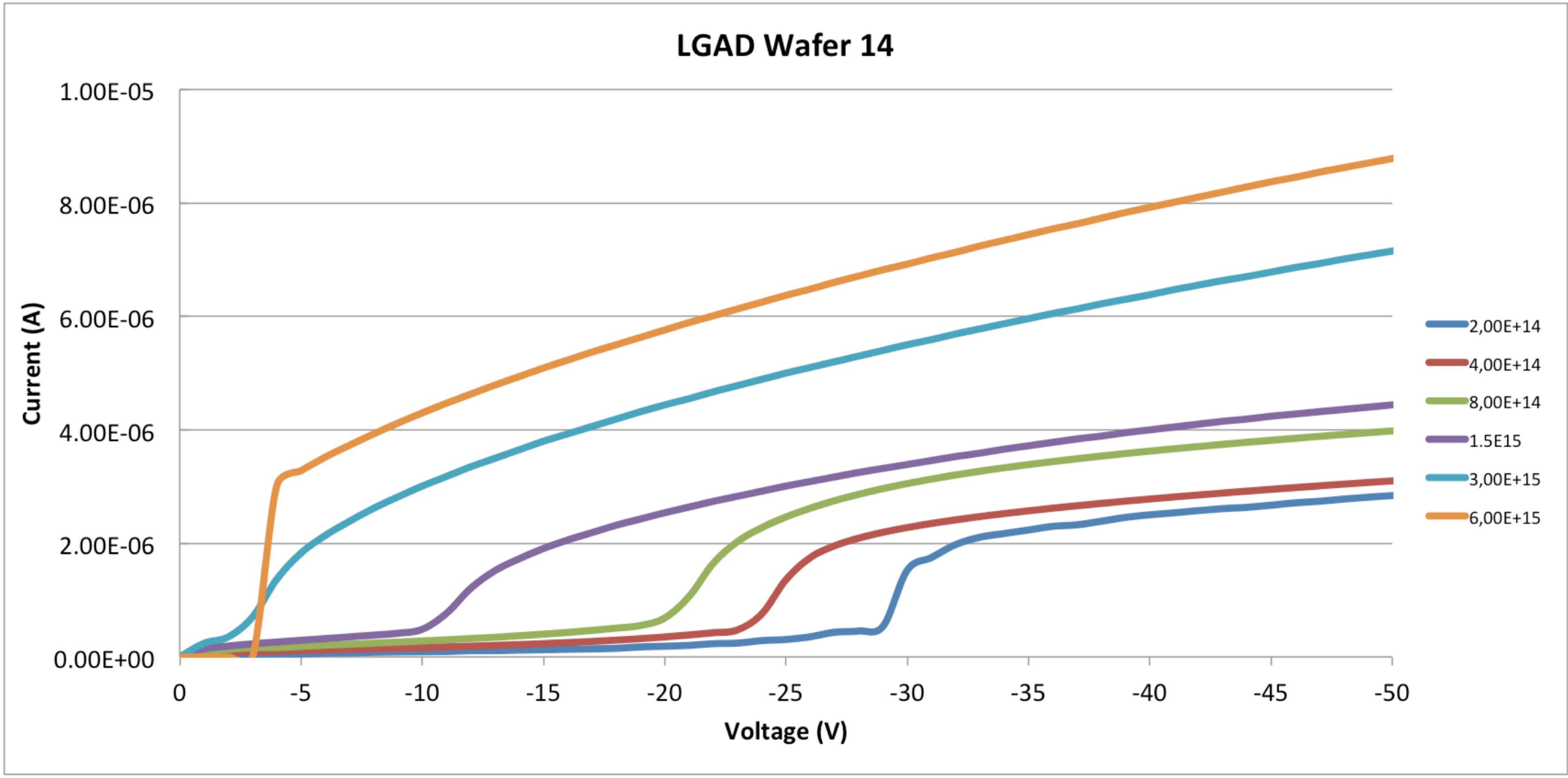
CV LGAD vs PiN

Perché sono diverse?

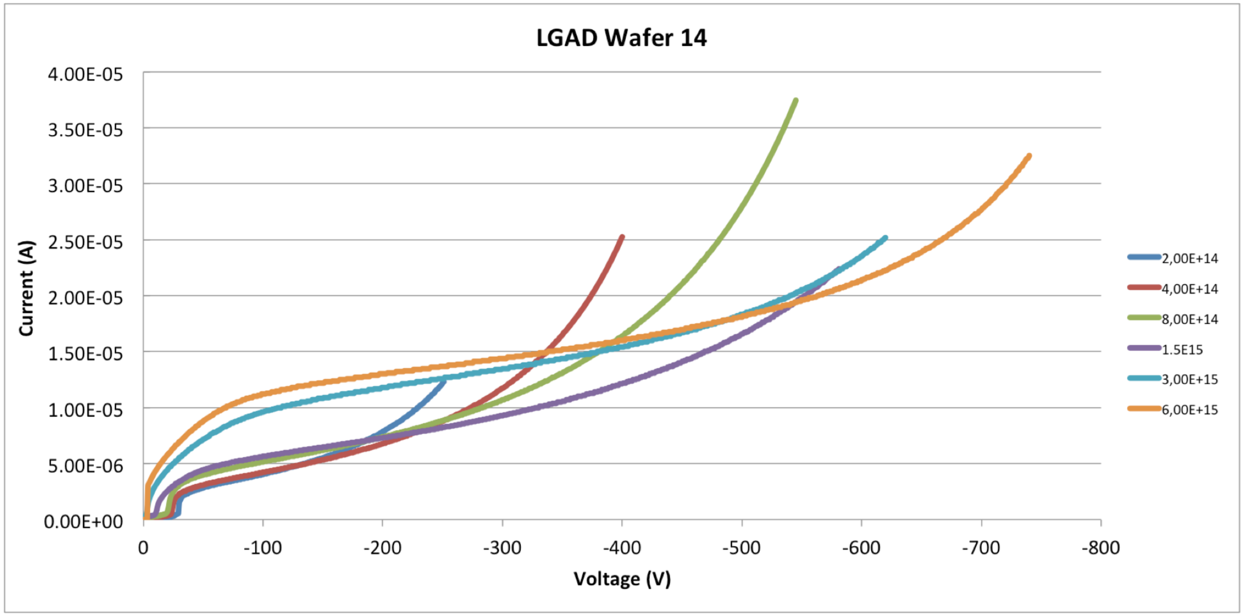


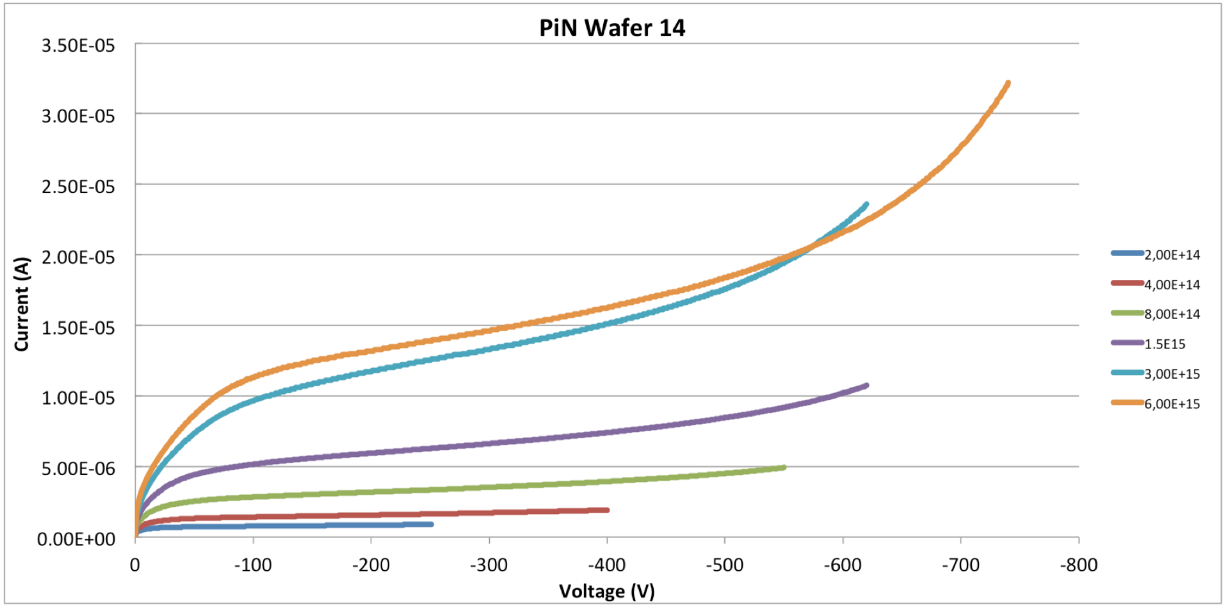


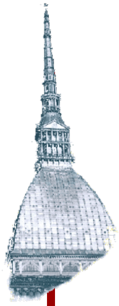
LGAD Current with radiation



PiN - LGAD Current (Wafer14-Gallium 1.04)







UFSD – Summary

We are just starting to understand the timing capability of UFSD

- Low-gain avalanche diodes offer silicon sensors with an enhanced signal amplitude
- The internal gain makes them ideal for accurate timing studies
- We developed a program, **Weightfield2** to simulate the behaviors of LGAD and optimized them for fast timing (available at http://personalpages.to.infn.it/~cartigli/Weightfield2.0/)
- **Thin detectors enhance the effect of gain, several productions in progress**

Sensor and electronics

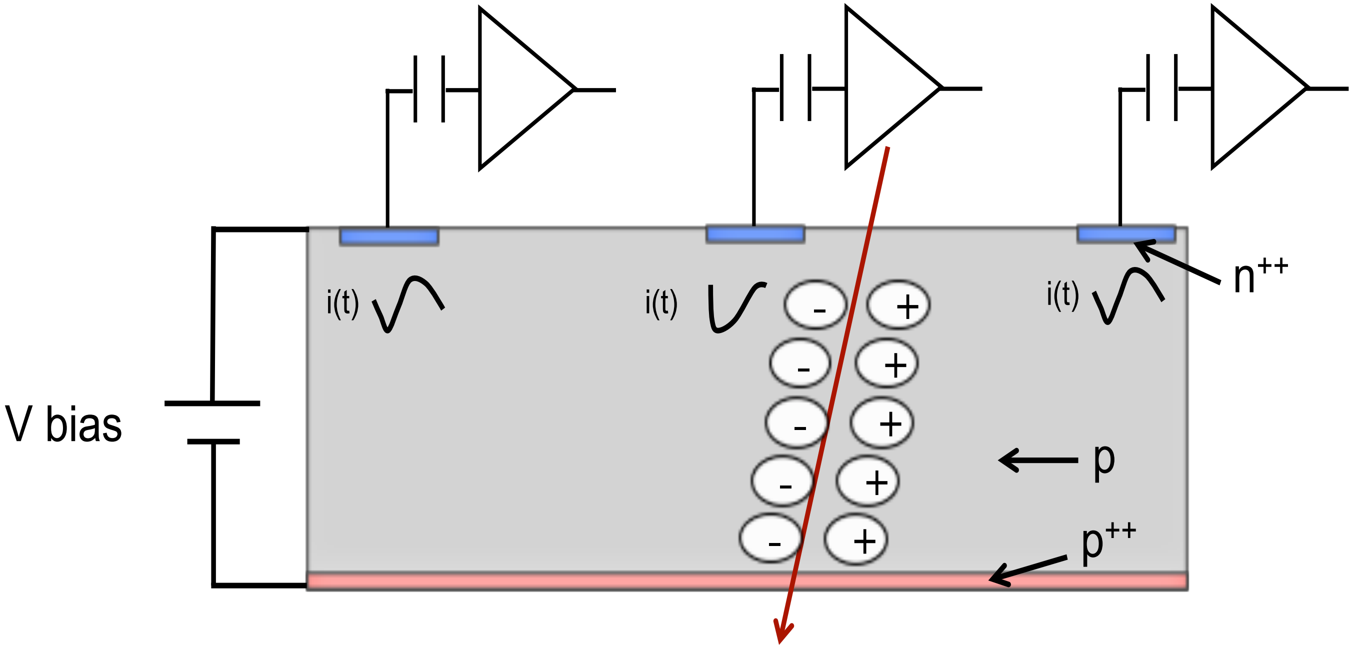


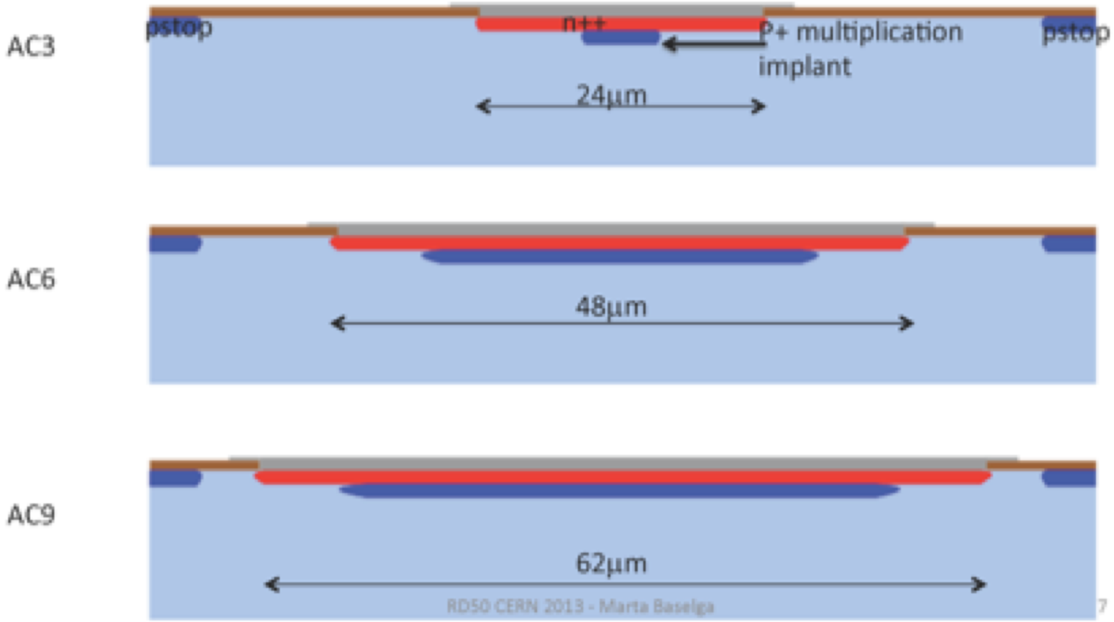
Figure 5 Basic operational principles of a silicon detector: an external bias voltage polarizes the p-n junction inversely, creating a large depleted volume. When an incident charged particle crosses the sensor, it creates electron-hole pairs whose drift generates an induced current in the electronics.

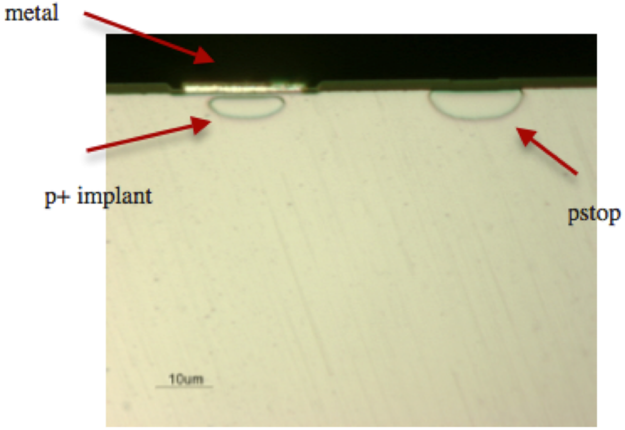
particle crosses the sensor, it creates by ionization along its path electron-hole pairs, on average 73 pairs in each micron.

LGADs Pads, Pixels and Strips

The LGAD approach can be extended to any silicon structure, not just pads.

This is an example of LGAD strips





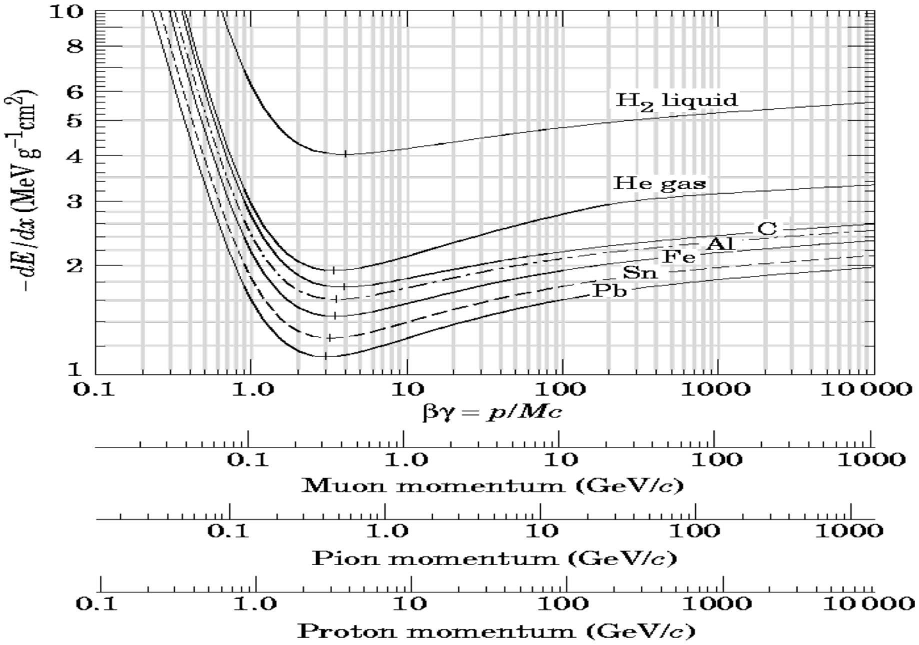
Energy deposition in Silicon Detectors

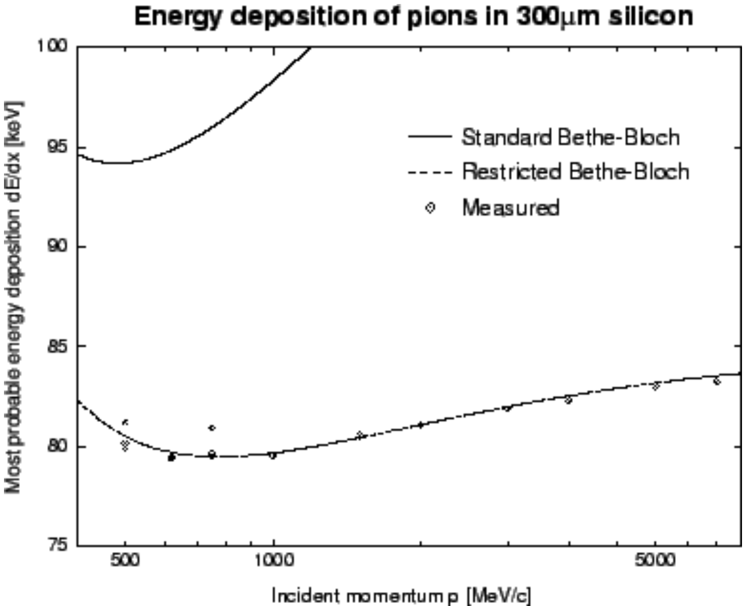
A charged particle looses energy in silicon, with a **mean energy of ~ 80 keV in 300 micron.**

The energy to create an **e/h pair is 3.6 eV**

80 keV/3.6 = 22,000 e/h pair

➔ 75 e/h pair per micron





Time Resolution and slew rate

Using the expressions in the previous page, we can write

$$\sigma_t^2 = \left(\left[\frac{V_{th}}{S/t_r}\right]_{RMS}\right)^2 + \left(\frac{N}{S/t_r}\right)^2 + \left(\frac{TDC_{bin}}{\sqrt{12}}\right)^2$$

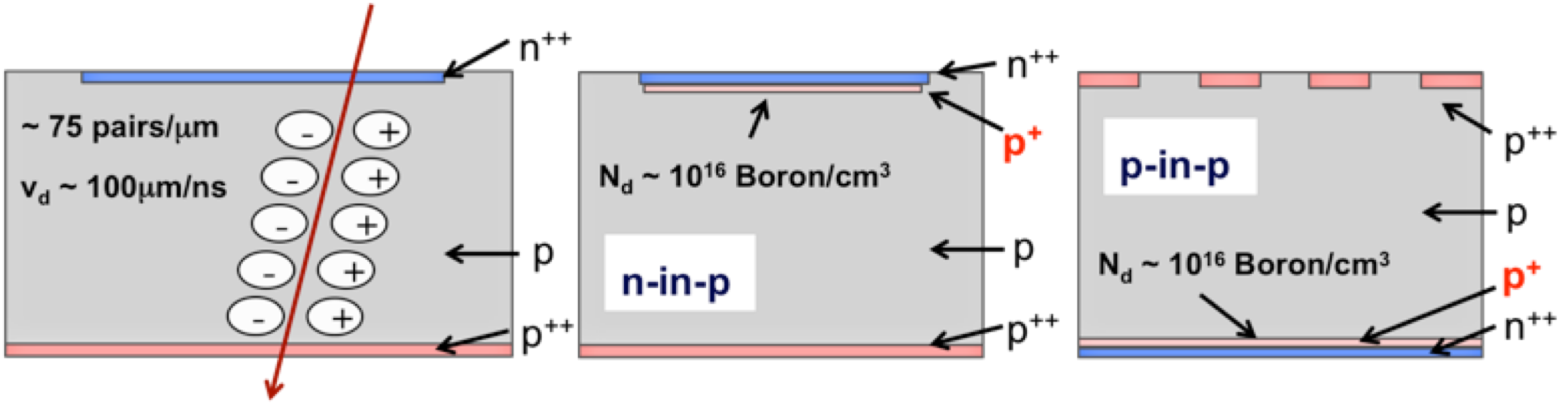
where:

- $S/t_r = dV/dt$ = slew rate
- N = system noise
- $V_{th} = 10\,N$

Assuming constant noise, to minimize time resolution
we need to maximize the S/t_r term
(i.e. the slew rate dV/dt of the signal)

➔ We need large and short signals ←

LGAD - Ultra-Fast Silicon Detector

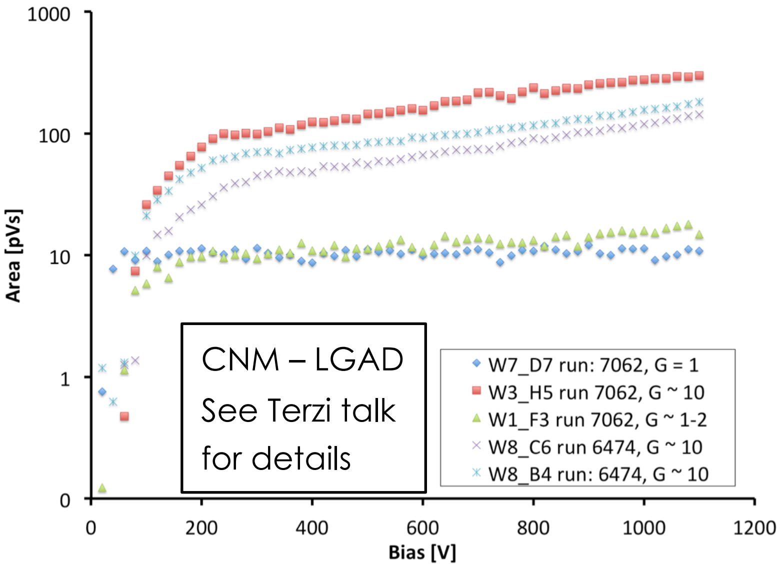


Traditional Silicon Detector **Ultra-Fast Silicon Detector**

Adding a highly doped, thin layer of of p-implant near the p-n junction creates a high electric field that accelerates the electrons enough to start multiplication. Same principle of APD, but with much lower gain.

Gain changes very smoothly with bias voltage.

Easy to set the value of gain requested.



CNM – LGAD
See Terzi talk
for details

The "Low-Gain Avalanche Detector" project

Is it possible to manufacture a silicon detector that looks like a normal pixel or strip sensor, but with a much larger signal (RD50)?

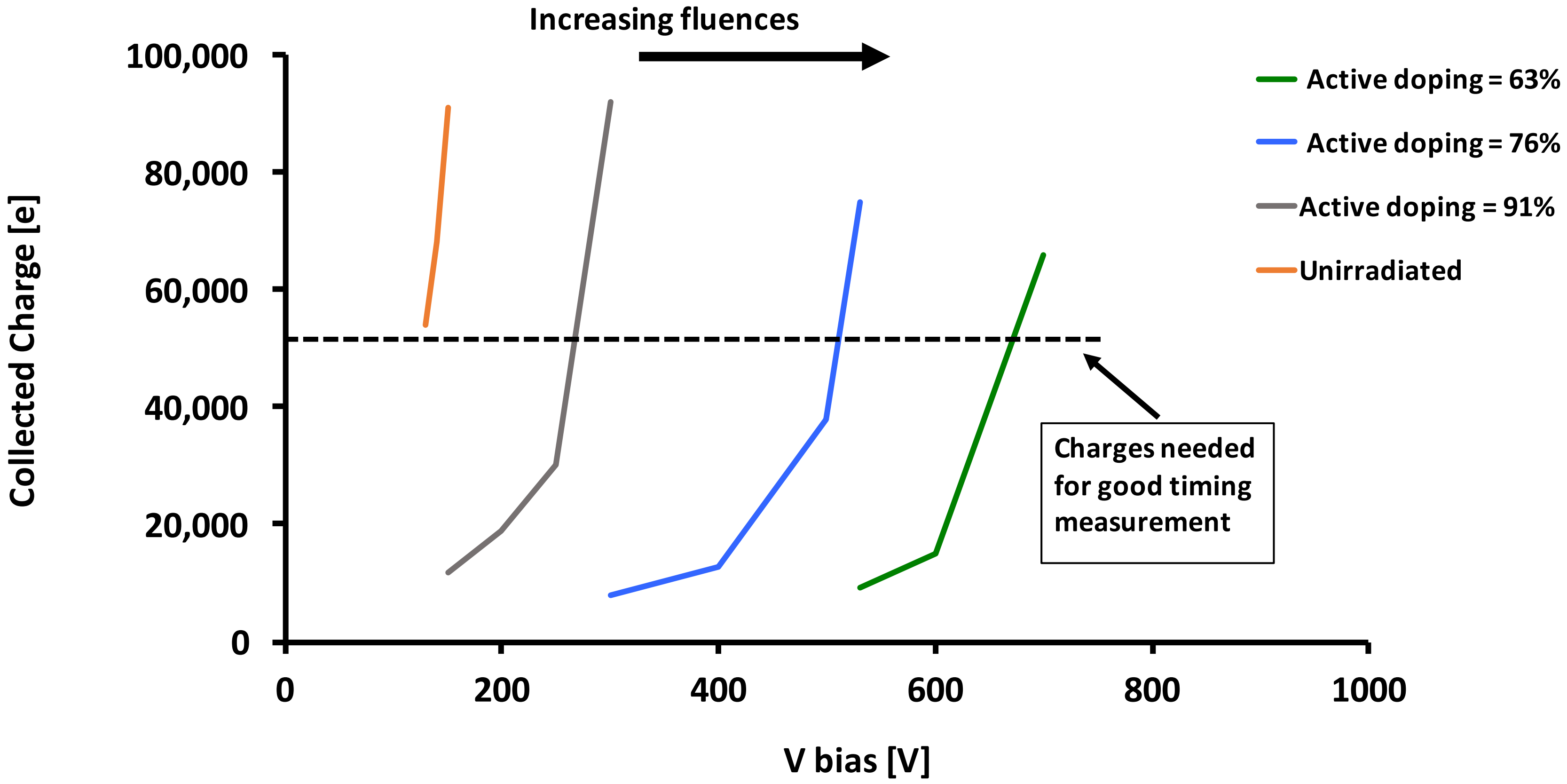
- 750 e/h pair per micron instead of 75 e/h?
- Finely Segmented
- Radiation hard
- No dead time
- Very low noise (low shot noise)
- No cross talk
- Insensitive to single, low-energy photon

Many applications:

- Low material budget (30 micron == 300 micron)
- Excellent immunity to charge trapping (larger signal, shorter drift path)
- Very good S/N: 5-10 times better than current detectors
- Good timing capability (large signal, short drift time)

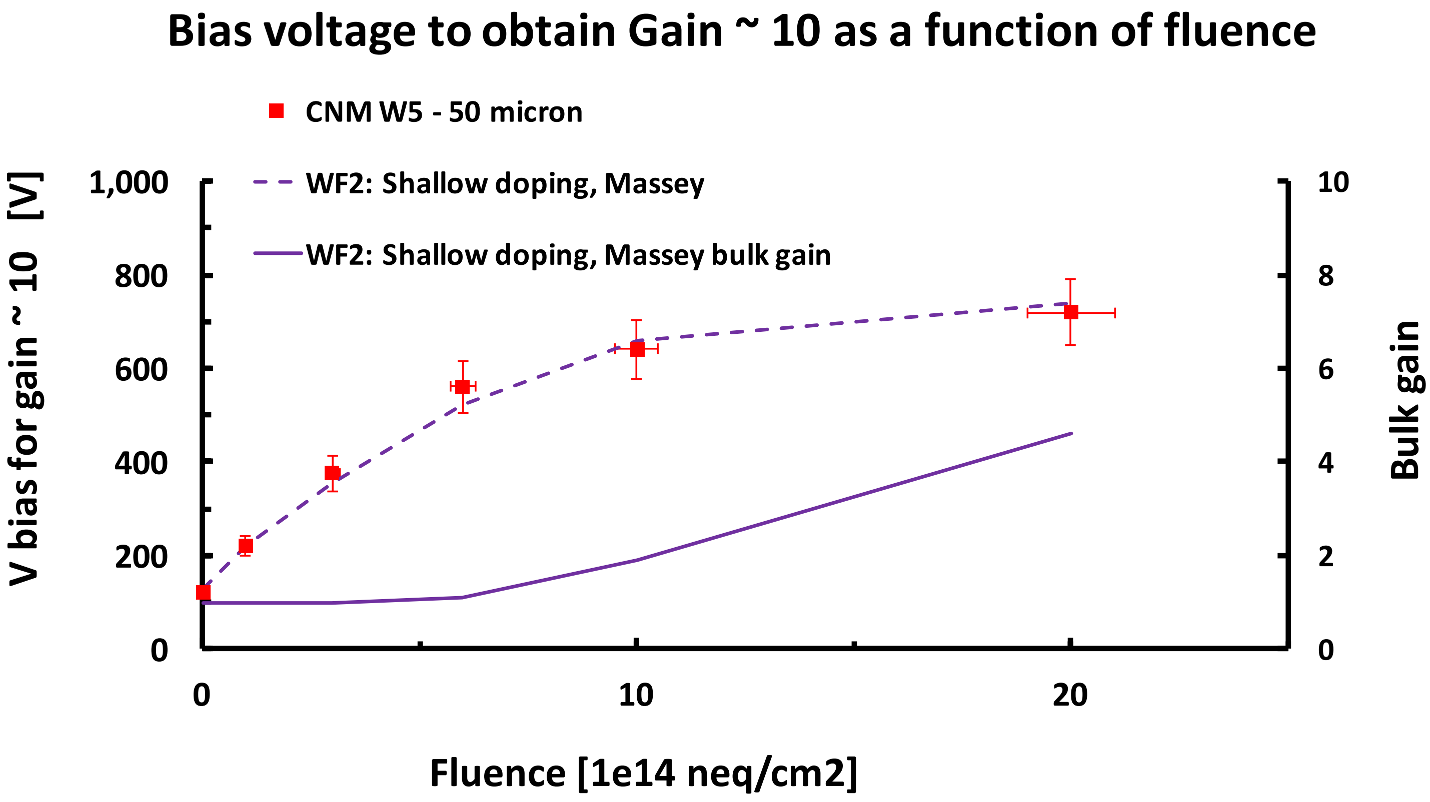
Compensation with Vbias

The necessary field can be recovered by increasing the external Vbias: proven to work up to 5 10^{15} n^{eq}/cm^2



How to use UFSD up to 5~10^{15} n_{eq}/cm^2

As the gain layer density decreases, we need to increase the external voltages to create the Efield needed for multiplications. In so doing, the gain moves from the gain layer to the bulk



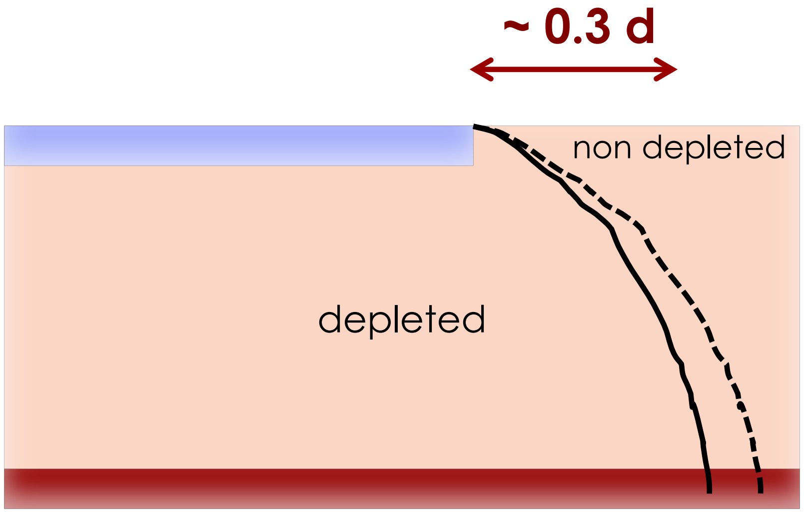
Sensor thickness and slim edge

Rule: when the depletion volume reaches the edge, you have electrical breakdown.

It's customary to assume that the field extends on the side by ~ 1/3 of the thickness.

edge = k* thickness

- k = 1 very safe
- k = 0.5 quite safe
- K = 0.3 limit



By construction, thin detectors (~ 100 micron) might have therefore slim edge